

M16C/Tiny Series

Rewriting the User ROM Area in EW0 Mode

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1. Abstract

This application note presents a method for rewriting the flash memory in EW0 mode of the M16C/Tiny-series microcomputers.

2. Introduction

The example application presented here is intended for use in the following type of microcomputer. Applicable microcomputer: Flash memory version of M16C/Tiny-series microcomputers

This sample program may also be used in other M16C-family microcomputers that have the SFR (Special Function Registers) similar to those in the M16C/Tiny series. However, since it is possible that some functions of your microcomputer will have been altered for functional enhancements, etc., please consult the user's manual for confirmation. Note also that careful evaluation is required before the sample program in this application note can be used.

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3. Explanation of Example Usage

3.1 Overview

The M16C/Tiny series has a special mode known as CPU rewrite mode in which the user ROM area can be rewritten from the CPU by executing software commands. This mode consists of two modes: EW0 and EW1.

EW0 mode

Advantages : The CPU continues operating even while programming and erasing.

: Interrupts generated while programming or erasing are responded quickly. (This applies when the interrupt handler routines are located in the RAM.)

Disadvantages: The flash memory program cannot be executed while programming or

erasing.

(Flash memory cannot be accessed for read.)

: A large amount of RAM is used.

(The programming/erasing routines must be located in the RAM.)

• EW1 mode

Advantages : The amount of RAM used is small.

(The programming/erasing routines can be located in the flash memory.)

Disadvantages: The CPU remains idle (in hold state) while programming and erasing.

: Interrupts generated while programming or erasing cannot be responded

quickly.

(The response time in the M16C/26, for example, is 100 μ s typ. during

programming and 8 ms max. during erasing.)

In this application note, a description is made of the programming procedure in EW0 mode, showing how to read/write and erase the flash memory.

The procedure described in the following pages will help you understand how to rewrite the flash memory in EW0 mode of the M16C/Tiny-series microcomputers.

• Rewriting operation specifications (for the M16C/26)

Rewrite mode	EW0
Operating CPU frequency during	10 MHz Note
rewrite	
Programming time (2 bytes)	75 μs, typ.
Erase time, 2 Kbyte block	0.2 s, typ.
Erase operation to erase suspend	8 ms, max.
transition time	

Note: For details about limitations on the on-chip oscillator and PLL, refer to Section 3.5.1, "Auto Program and Auto Erase Procedure."

These limitations apply to flash memory rewrite operation in CPU rewrite mode, and not to normal operation of the microcomputer.

3.2 About Flash Memory

Flash memory is electrically programmable and erasable nonvolatile memory.

The following shows the manner in which the flash memory of the M16C/Tiny series is accessed:

- The flash memory can be programmed in units of one word.
- The flash memory is erased in block units.
- The flash memory cannot be accessed for read during programming and erasing.

3.2.1 Operations on Flash Memory

The following shows operations performed on flash memory.

Table 3-1. Operations and Limitations on Flash Memory

Operation	Description of operation	Limitation	
name			
Read	Means reading out written data.	Any blocks cannot be accessed for read	
		while programming and erasing.	
Write	Means changing bit value from 1 to 0.	Only blank addresses can be written to.	
Erase Means changing bit value in the entire		Must be performed in block units.	
	block to 1 (changed all to FF ₁₆).		

The following shows how to resolve the limitations imposed on data rewrite operation of flash memory.

Table 3-2. Flash Memory Limitations and How to Resolve

Limitation	Solution	
Flash memory cannot be	Locate the programming/erasing routines in other than the flash	
accessed for read while	memory.	
programming and erasing.	(EW0 mode)	
(Programs cannot be run in	The CPU automatically halts while programming or erasing, unable to	
flash memory.)	read from flash memory.	
	(EW1 mode)	
Flash memory can only be	Devise the data retention method so as to reduce the number of times	
erased in block units.	the flash memory needs to be erased. Note	

Note: This method is not discussed in this application note.

This application note uses EW0 mode and the software in the RAM to rewrite the flash memory.

3.3 Rewriting the Flash Memory in EW0 Mode

3.3.1 EW0 Mode

EW0 mode allows the user ROM area to be rewritten by issuing the programming (Auto Program) and erasing (Auto Erase) commands from the program located in the RAM. The CPU continues operating even during Auto Program and Auto Erase.

The interrupts whose vectors are accommodated in the variable vector table can be made usable by moving the vectors and the interrupt handler routines into the RAM area.

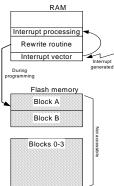


Figure 3-1. Conceptual Diagram of Auto Program Operation

Auto Erase has an "erase suspend" function. The erase suspend function means suspending the auto erase processing during Auto Erase to read data from the flash memory. In order for the erase suspend function to be controlled during EW0 mode, the registers associated with it must be set up in software. For details, refer to Section 3.5, "EW0 Auto Program and Auto Erase Procedure."

During erase suspend mode, it is possible to call a process located in the flash memory or read data out of the flash memory.

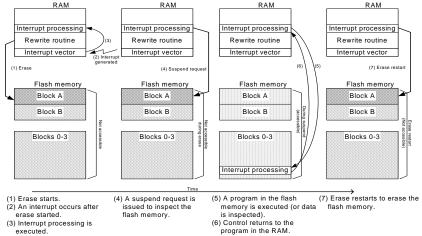


Figure 3-2. Conceptual Diagram of Auto Erase Operation

In EW0 mode, unlike in EW1 mode, the CPU continues operating even during Auto Erase or Auto Program, so that interrupts generated during that time can be responded to as quickly as in normal operation. However, a finite amount of space must be provided in the RAM for the rewrite routine, variable vector table and the relevant interrupt handler routines to be able to work. In addition, program transfer processing is needed.

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3.3.2 Flash Memory Mode Transition

The flash memory control registers and software commands are used to control the flash memory in the M16C/Tiny series of microcomputers.

Software commands are generated by writing to the flash memory.

The diagram below shows operation modes of the flash memory during EW0 mode.

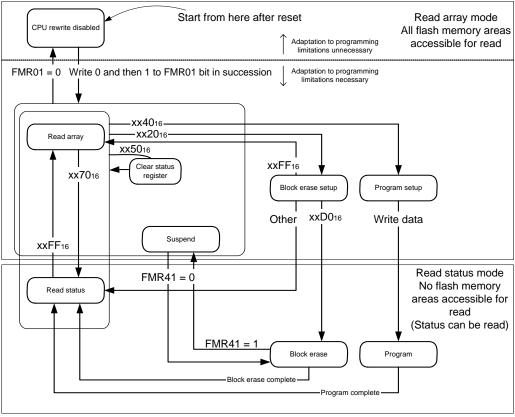


Figure 3-3. Flash Memory Operation Modes

In Figure 3-3, "Flash Memory Operation Modes," transitions of " $xx40_{16}$," etc. are software commands. "FMR41 = 0" means setting the indicated register bit to 0.

During EW0 mode, the flash memory can be placed in either read array mode where the written content can be read or status read mode where the status can be read.

Table 3-3. Flash Memory Read Modes

Read mode Feature	
Read array mode The written content can be read out.	
Read status mode	The status can be read from any area of the flash memory.
	The status indicates whether the flash memory is operating or in error.
	(Written content cannot be read out.)

While the flash memory is in read status mode, no programs can be run in the flash memory. This is because the program written to the flash memory cannot be read out during read status mode.

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3.3.3 Interrupts during Flash Memory Rewrite

If the erase suspend function is used in EW1 mode, be aware that the erase operation performed differs depending on the type of interrupt used (maskable interrupt or nonmaskable interrupt). During programming too, if interrupts are used in other than byte write, the programming operation performed differs depending on the type of interrupt used, as for the erase operation.

Operational differences due to the type of interrupt are outlined below.

Table 3-4. Auto Erase/Auto Program and Interrupt Operation

Mode	State	When a maskable	When a nonmaskable interrupt (NMI interrupt,
		interrupt is accepted	watchdog timer, oscillation stoppage detection or
			voltage detection interrupt) is accepted
EW0	During auto	Maskable interrupts can	When an interrupt request is accepted, auto erase or
	erase	be used (and serviced) by	auto program is forcibly stopped and the flash
		locating their vectors in	memory is reset. When the flash memory restarts a
		the RAM.	certain time later, the CPU starts processing the
			interrupt.
	During auto		Since auto erase or auto program is forcibly stopped,
	program		correct values may not be read from the block that
			was being erased or the address that was being
			programmed. Therefore, execute auto erase/auto
			program again after the flash memory has restarted
			and confirm that the operation is terminated
			normally.
			The watchdog timer remains idle during command
			execution.

Note 1: The vector for the address match interrupt is located in the ROM. Do not use it while executing an erase/program command.

Note 2: Since the fixed vectors are located in block 0, do not use nonmaskable interrupts while auto-erasing block 0.

3.4 EW0 Auto Program and Auto Erase Procedure

3.4.1 Auto Program and Auto Erase Procedure

The following shows an auto program flowchart following the procedure described in the manual. This flowchart is shown for comparison with the auto program procedure for the RAM-reduced version, and not a flowchart for the sample program. For details about the sample program flowchart, refer to Figure 3-11, "RAM Reduced Version Auto Program Flowchart".

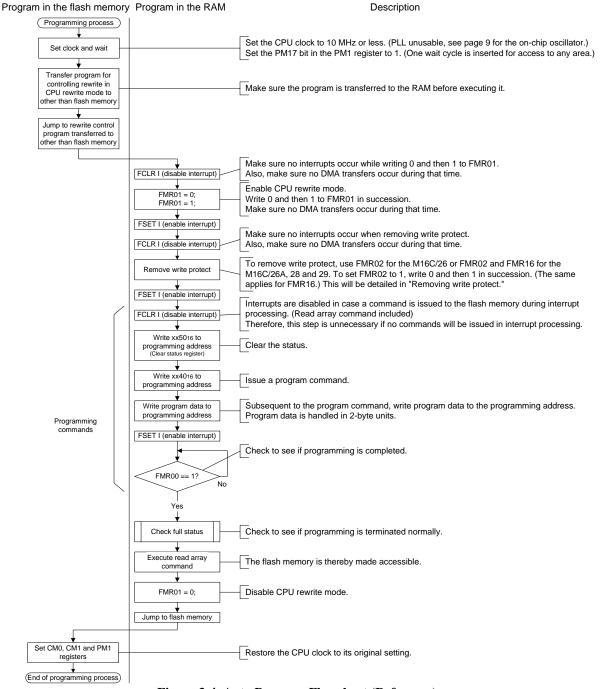


Figure 3-4. Auto Program Flowchart (Reference)

The following shows an auto erase flowchart following the procedure described in the manual. This flowchart is shown for comparison with the auto program procedure for the RAM-reduced version, and not a flowchart for the sample program. For details about the sample program flowchart, refer to Figure 3-12, "RAM Reduced Version Auto Erase Flowchart".

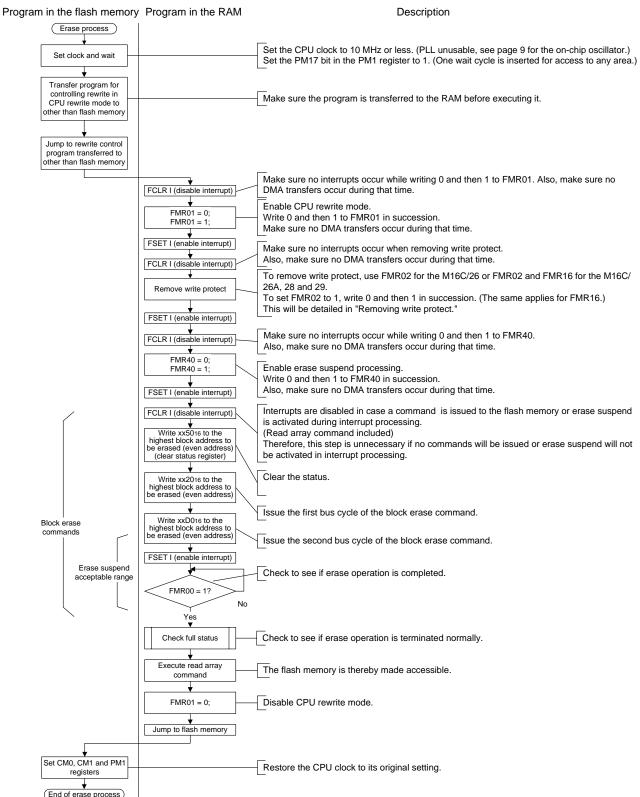


Figure 3-5. Auto Erase Flowchart (Reference)

The following shows an erase suspend flowchart.

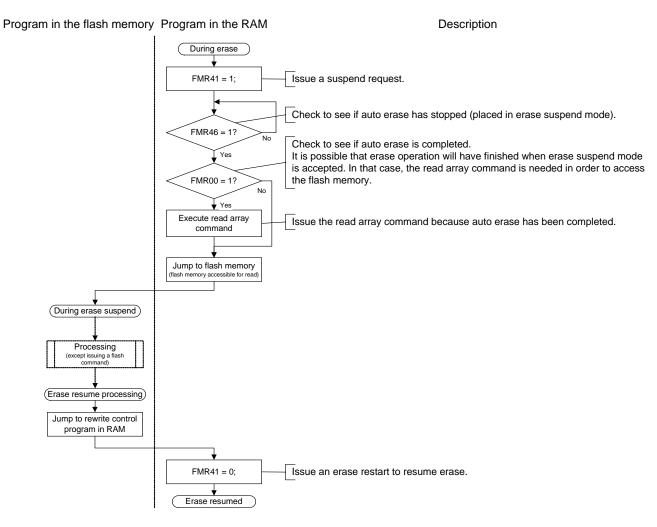


Figure 3-6. Erase Suspend Processing Flowchart

The flowcharts shown in the preceding pages are described in detail below.

• Setting clock and wait

When the flash memory is placed in CPU rewrite mode (by setting FMR01 to 1), the following limitations apply.

- · A wait cycle must be inserted for access to any ROM and RAM area (by setting PM17 to 1).
- The CPU clock must satisfy the conditions below.

Table 3-5. Clock Limitations for CPU Rewrite Mode

Operating clocks	Limitations	Remarks
Main clock	10 MHz or less	Set by CM0 and CM1.
On-chip oscillator	f1 (ROC),	Set by ROCR.
(M16C/26A, 28 and 29)	f2 (ROC) or	
	f3 (ROC) and the ROCR	
	register is set to divide by 4	
	or 8.	
PLL clock	Unusable	Change from the PLL clock to the main
(M16C/26A, 28 and 29)		clock using the system clock control bit
		(CM11) in System Clock Control Register 1
		(CM1).
		There is no need to stop the operation of the
		PLL frequency synthesizer.

Furthermore, if blocks A and B are rewritten 100 times or more, blocks A and B must be accessed for read with one wait cycle by setting FMR17 to 1, even in other than CPU rewrite mode. These are summarized below.

Table 3-6. CPU Rewrite Mode and Limitations

	State	Clock limitations	Use of PLL	Wait
CPU rewrite mode Read from any block		Yes	Unusable	Necessary
enabled	Issuance of software			
	command			
CPU rewrite mode	Read from blocks A and B	No	Usable	Unnecessary
disabled	(Rewritten less than 100			
	times)			
	Read from blocks A and B	No	Usable	Necessary
	(Rewritten 100 times or			
	more)			
	Read from any blocks other	No	Usable	Unnecessary
	than A and B			

Limitations on the CPU clock can be lifted during erase suspend. To remove limitations on the CPU clock, reset the CPU rewrite mode select bit (FMR01) to 0 (disable) during erase suspend. The erase suspend state is retained intact even when CPU rewrite mode is disabled.

To resume auto erase, set up registers, etc. to meet conditions for CPU rewrite mode, enable CPU rewrite mode, and then clear the erase suspend request bit (FMR14) to 0 (erase restart).

An example operation is shown below.

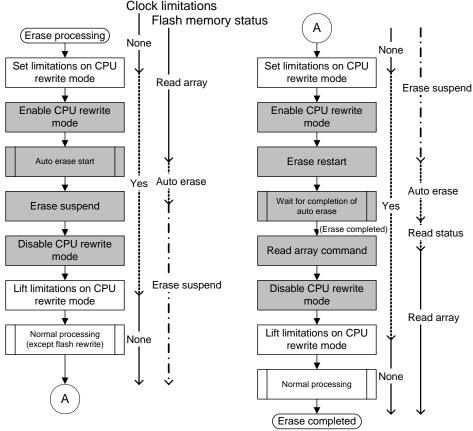


Figure 3-7. Clock Control during Erase Suspend

- Transferring a program to the RAM area Refer to Section 3.7, "About Programs Running in the RAM Area."
- Entering CPU rewrite mode

Set bit 1 (FMR01) in Flash Memory Control Register 0 (FMR0).

To set the FMR01 bit to 1, write 0 and then 1 in succession. Make sure no interrupts or DMA transfers occur before writing 1 after writing 0.

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Removing write protect

Some areas must have their write protect removed before they can be rewritten.

To remove write protect, the FMR02 and FMR16 bits (M16C/26A, 28 and 29) must be set.

The tables below show how write protect is set for each type of microcomputer.

Table 3-7. Write Protect Set for the M16C/26

Register settings	Rewrite areas		
FMR02	Blocks A and B Blocks 0 and 1 Other block		
0	0	×	0
1	0	0	0

O: Rewritable X: Not rewritable (write protected)

Table 3-8. Write Protect Set for the M16C/26A, 28 and 29

Register settings		Rewrite areas		
FMR16	FMR02	Blocks A and B	Blocks 0 and 1	Other blocks
0	0	0	×	×
0	1	0	×	×
1	0	0	×	0
1	1	0	0	0

O: Rewritable X: Not rewritable (write protected)

The following shows how to set FMR02 and FMR16.

Table 3-9. How to Set FMR02 and FMR16

Bit name	If FMR01 bit = 0	If FMR01 bit = 1
FMR02	Always 0	Can be set.
		To set the bit to 1, write 0 and then 1 in succession. Note
FMR16	FMR16 Cannot be set. Can be set.	
	(Value retained)	To set the bit to 1, write 0 and then 1 in succession. Note

Note: Make sure no interrupts or DMA transfers occur before writing 1 after writing 0.

The data areas (blocks A and B) have an access enable bit (PM10). Set the PM10 bit to 1 when accessing the data area for read. When CPU rewrite mode is enabled (FMR01 = 1), the PM10 bit is automatically set to 1. For this reason, blocks A and B do not have write protect.

For details about the PM10 bit, refer to Section 3.6, "Readout Procedure."

As shown in Table 3-9, the FMR02 bit retains its value only when CPU rewrite mode is enabled (FMR01 bit = 1), whereas the FMR16 bit always retains its value regardless of whether CPU rewrite mode is enabled or not.

In the sample program, therefore, FMR02 and MFR16 are set in the processing described below.

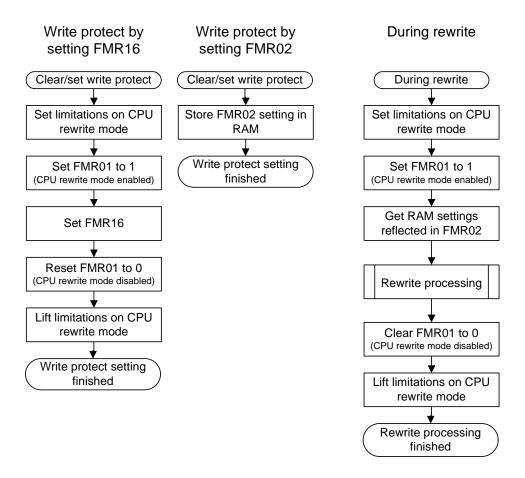


Figure 3-8. Write Protect Settings in the Sample Program

In the sample program, the "write protect setting" interface function and the "rewrite" interface function are separated.

The FMR16 bit has its value retained even when CPU rewrite mode is disabled (FMR01 bit = 0). On the other hand, the FMR02 bit has its value not retained and changed to 0 when CPU rewrite mode is disabled (FMR01 bit = 0).

The FMR16 bit is set in the "write protect setting" interface function. The FMR02 bit is set up back again from its last set content during rewrite.

Before the "rewrite" interface function can be called, the "write protect setting" interface function must be called in order to remove write protect. The write protect information once set remains effective unless it is set again in the "write protect setting" interface function.

Program command

This command writes data to the flash memory one word (two bytes) at a time.

When the program command is issued, the CPU auto-programs the flash memory (by writing program data and verifying).

The auto program operation is depicted below.

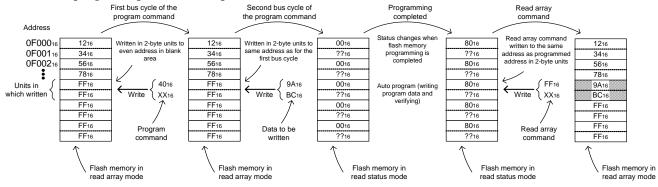


Figure 3-9. Auto Program Procedure

Make sure the command is written in 16-bit units to the even addresses in the user ROM area. For details about the change of flash memory modes after the CPU started programming the flash memory, refer to Figure 3-3, "Flash Memory Operation Modes."

Erase command

This command erases data from the flash memory in block units.

When the erase command is issued, the CPU auto-erases the flash memory (by erasing data and verifying).

The auto erase operation is depicted below.

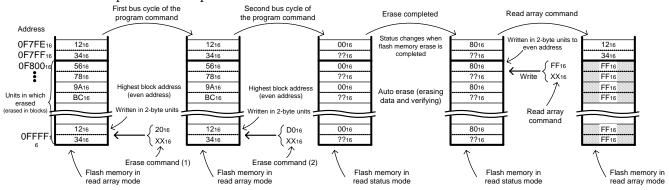


Figure 3-10. Auto Erase Procedure

Make sure the command is written in 16-bit units to the even addresses in the user ROM area. For details about the change of flash memory modes after the CPU started erasing the flash memory, refer to Figure 3-3, "Flash Memory Operation Modes."

Full status check

To confirm whether auto program or auto erase has been executed normally, inspect the FMR06 and FMR07 bits.

The table below shows the relationship between the status register status and errors.

Table 3-10. Status of the FMR0 Register and Errors

Status of the FMR00 register (status register) FMR07 FMR06		Error	Error occurrence conditions
1	1	Command sequence error	 When the command was not written correctly When invalid data (not "xxD0₁₆" or "xxFF₁₆) was written in the second bus cycle of the block erase command Note 1 When the block erase command was executed on a write protected block. When the program command was executed on a write protected block.
1	0	Erase error	• When the block erase command was executed on a write "enabled" block, but the block was not auto-erased correctly
0	1	Program error	• When the program command was executed on a write "enabled" block, but the block was not auto-programmed correctly
0	0	No error	Successfully executed.

Note 1: Writing "xxFF₁₆" in the second bus cycle of these commands places the flash memory into read array mode, in which case the command code written in the first bus cycle is invalidated.

Read array command

This command places the flash memory into read array mode.

In read array mode, the content recorded in the flash memory can be read out.

The flash memory is placed into read array mode by writing "xxFF16" in the first bus cycle. Then, when the address from which to read is entered in the next or the subsequent bus cycle, the content of the specified address can be read out in 16-bit units.

Read array mode is retained intact until another command is written to the flash memory, the contents of multiple addresses can be read out successively.

Disabling CPU rewrite mode

Reset bit 1 (FMR01) in Flash Memory Control Register 0 (FMR0) to 0.

Erase suspend

To use the erase suspend function in EW0 mode, set the erase suspend request bit (FMR41 bit in the FMR4 register) to 1, and then check the erase status bit (FMR46 bit in the FMR4 register) to see that the flash memory is placed into erase suspend mode.

The FMR46 bit is 0 during auto erase operation, and set to 1 when auto erase has stopped (placed into erase suspend mode).

If the flash memory is placed into erase suspend mode at the same time auto erase has finished, issue the read array command before accessing the flash memory.

During erase suspend mode, it is possible to call a process residing in the flash memory or read data out of the flash memory.

To resume auto erase, clear the erase suspend request bit (FMR41 bit in the FMR4 register) to 0 from the program in the RAM.

• About differences between microcomputers in the M16C/Tiny series
The M16C/26, 26A, 28 and 29 differ in the following points with respect to the flash memory related features.

Table 3-11. Differences between the M16C/26, 26A, 28 and 29 with respect to the flash memory related features

Item	M16C/26	M16C/26A	M16C/28	M16C/29
Write protect	Write protected by FMR02	Write protected by FMR16 and FMR02	←	←
FMR16 included or not	Not included	Included	←	←
PLL included or not, and PLL based	PLL not	PLL based rewriting	←	←
rewriting	included	prohibited	_	_

3.4.2 Reducing the RAM Size

To reduce the RAM size used by a program, separate processes into those that can be and those that cannot be run in the flash memory area, and then move the processes that do not need to be run in the RAM into the flash memory area.

It is only when the flash memory is in read status mode (including cases where auto program or auto erase is underway) that processes need to be run in the RAM.

Alter the following contents from the procedure described in Section 3.5.1, "Auto Program and Auto Erase Procedure," to reduce the RAM size.

When programming the flash memory

Run all processing up to immediately preceding the first bus cycle of the program command in the flash memory.

Perform operations from the first bus cycle of the program command to check for completion of programming in the RAM. (No changes needed)

To perform full status check, place the flash memory back into read array mode prior to the full status check.

Perform full status check in the flash memory.

When erasing the flash memory

Run all processing up to immediately preceding the first bus cycle of the erase command in the flash memory.

Perform operations from the first bus cycle of the erase command to check for completion of auto erase in the RAM. (No changes needed)

To perform full status check, place the flash memory back into read array mode prior to the full status check.

Perform full status check in the flash memory.

Next, a flowchart with the above contents incorporated will be shown.

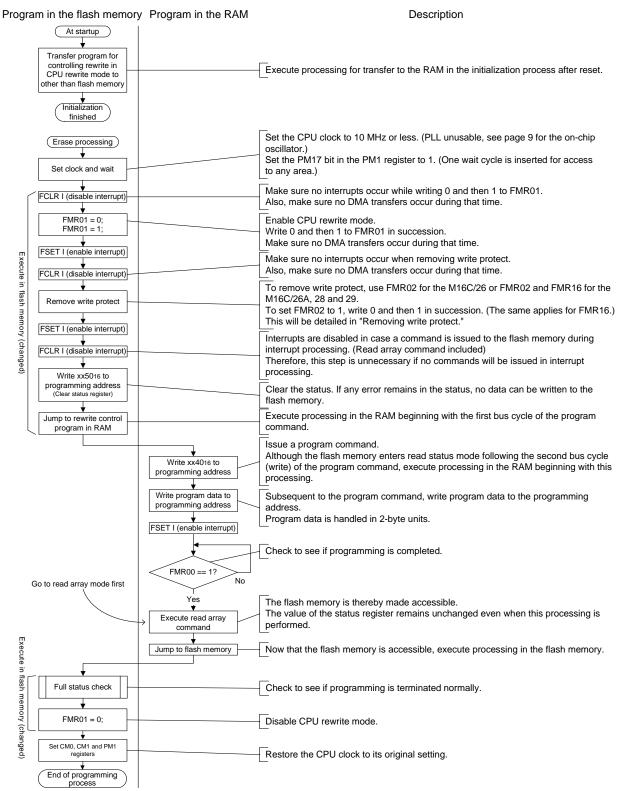


Figure 3-11. Auto Program Flowchart for the RAM Reduced Version

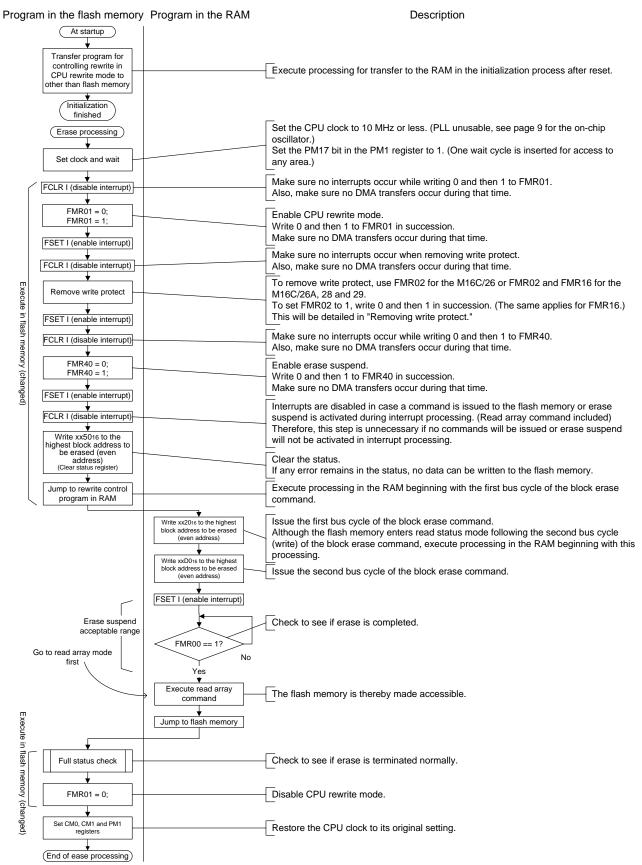


Figure 3-12. Auto Erase Flowchart for the RAM Reduced Version

In the sample program, the auto erase procedure consists of the processing shown above plus erase suspend processing based on the erase suspend function.

3.5 Readout Procedure

The flash memory can be accessed for data readout during read array mode.

Writing "xxFF₁₆" in the first bus cycle places the flash memory into read array mode. (When the program is running in the flash memory, read array mode is already entered into. When the flash memory is being rewritten following the procedure described in this application note, it is placed into read array mode when a programming process is completed.)

Furthermore, before data can be read from the data area (block A or B), the data area access enable bit (PM10) in Processor Mode Register 1 (PM1) must be set to 1.

About the PM10 bit

- Set the PRC1 bit in the PRCR register to 1 (write enabled) before rewriting the PM10 bit.
- When CPU rewrite mode is enabled (FMR01 = 1), the PM10 bit is automatically set to 1.

Table 3-12. PM10 Bit and the Status of Blocks A and B

PM10	Status of blocks A and B		
0	Cannot be read (Always PM10 = 1 during rewrite)		
1	Can be read Can be rewritten		

In the sample program, the PM10 bit is set to 1 in the device initialization process.

3.6 Programs Running in the RAM Area

The sample program includes some programs that run in the RAM.

In the example below, the program data is stored in 0FB000₁₆ and is executed in the RAM.

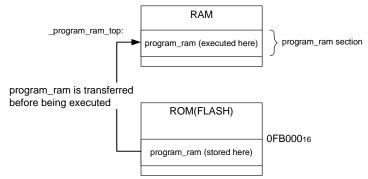


Figure 3-13. Program Location Diagram

3.6.1 Altering the Section Name

The following explains a method for adding another section named "program_ram" and locating in it a program that is to be run in the RAM.

To relocate the program from the program section into the program_ram section, write a program statement as follows:

```
void ThisProgramOnROM(void)
{
     /* This program is located in the program section. */
}
/* Defined after the #program SECTION declaration are located in program_ram. */
#pragma SECTION program program_ram
void ThisProgramOnRAM(void)
{
     /* This program is located in the program_ram section. */
}
```

Next, add to sect30.inc the program_ram section and a label description _program_ram_top at the beginning.

The position at which the program will be run is determined by sect30.inc. (In the example here, it is located after heap section.)

Note that _program_ram_top is used to transfer the program.

3.6.2 Transferring the Program

Next, write a program statement to transfer the program from the ROM to the RAM. In the example explained below, the program is transferred at startup.

Use the N_BCOPY macro to transfer the program from the far area to the near area or the BCOPY macro to transfer to the far area. (The N_BCOPY and BCOPY macros are defined in ncrt0.a30.) Add the transfer processing to the C language startup routine ncrt0.a30 by using this macro. The following shows an example in which N_BCOPY is used.

crt0.a30

3.6.3 Specifying Locations where the Program is Stored and Executed

The compiler must be directed to allocate separate addresses for the program at which it is to be stored and executed.

This can be accomplished by specifying an option in ln30 as shown below.

```
ln30 -LOC program_ram=0FB000
```

The above linker option -LOC specifies the address at which the data in the specified section should be stored by specifying the location of the program_ram section (program to be stored at the address $0FB000_{16}$).

Note: This option "-LOC" and the related option "-ORDER" cannot be specified in -ln30 for NC30. Make sure the option is set in ln30. The programs relocated by ALIGN specification may not always run normally. Therefore, if the beginning address of a relocated section is an even address, set an even address for the location to which the program is to be transferred. The same applies to odd addresses. (In the example here, the address specified by -LOC is set to an even address, and the ALIGN option is specified for the program_ram section, so that both sections will start on an even address.) This option only specifies the registered address of a set section, and does not have a function to transfer the program to its run-time address area. To call a process in the set section, be sure to transfer the desired process to the address set by the program before calling it.

3.6.4 Setting Vector Addresses in the RAM Area

Locate the interrupt vectors in the RAM.

Here, explanation is made of the following operations:

- Reserve storage for the variable vector table in the RAM.
- Copy the necessary variable vectors from vector_table which is included as a standard component.
- Copy them to the variable vectors in the RAM at startup..

First, in sect30.inc, reserve 4 bytes $\times 64 = 256$ bytes for the vector area in the RAM.

```
;-----;
RAM vector area;
.section vector_ram,data,ALIGN
.ALIGN
_vector_table:
.blkl 64
.glb _vector_table
```

At startup, copy the default interrupt vectors to the interrupt vectors in the RAM to alter the vector addresses. Add this setting to the startup routine ncrt0.a30.

```
;----
; vector area
;-----
N_BCOPY VECTOR_ADR,_vector_table,vector_ram
ldc #(_vector_table >> 16),INTBH
ldc #(_vector_table & 0FFFFh),INTBL
```

Note that since the contents described in Section 3.7, "About Programs Running in the RAM Area," all are written in the sample program, please refer to the sample program for details about the entire description.

4. Sample Program

The sample program explained here includes the content described in Section 3.5.2, "Reducing the RAM Size."

The sample program is written as a flash memory device driver.

Following are defined as the driver interfaces.

If an error occurs during flash memory auto program or auto erase, error code is returned. In such a case, please execute the processing described in the manual. (After executing the clear status command, reexecute auto program for a programming error or auto erase for an erase error up to three times repeatedly.)

Table 4-1. Function Table

Function Name	Description	Remark
StartEraseFlash()	Starts erasing flash memory.	Unusable in an interrupt. Interrupts are controlled using the I flag internally. If interrupts need to be disabled in order to use this function, disable interrupts in the IPL.
RestartEraseFlash()	Resumes suspended erase.	Unusable in an interrupt. Interrupts are controlled using the I flag internally. If interrupts need to be disabled in order to use this function, disable interrupts in the IPL.
WriteFlash()	Writes to flash memory.	Unusable in an interrupt. Interrupts are controlled using the I flag internally. If interrupts need to be disabled in order to use this function, disable interrupts in the IPL.
ReadFlash()	Reads from flash memory.	
UnlockBlockFlash()	Unlocks flash memory from write protect.	
LockBlockFlash()	Locks flash memory to write protect.	
SuspendErase()	Issues an event requesting that flash memory erase be suspended	If this function is called after calling the StartEraseFlash() function, StartEraseFlash() suspends the erase operation and returns with F_SUSPEND. Thereafter, the erase operation is resumed by RestartEraseFlash(). (At this time, the erase operation will be suspended again by SuspendErase().)
ResumErase ()	Cancels an event requesting that flash memory erase be suspended	If this function is called after calling the SuspendErase() function, the request to suspend erase operation issued by SuspendErase() is canceled.
SuspendFlash()	Suspends erasing flash memory.	Used for interrupts only. If this function is called while the flash memory is being erased, the flash memory goes to an erase-suspended state. After return from this function, the flash memory can be accessed for read.
ResumFlash()	Cancels suspended erase of flash memory	Used for interrupts only. This function is called only when the flash memory placed in an erase-suspended state by SuspendFlash() needs to be erased again from where it stopped from the beginning.

4.1 File Configuration

The sample program is comprised of the files listed below.

Table 4-2. File Configuration Table

File Name	Description
flashdevconf.h	This file sets up the driver.
flashdevdrv.h	This header file is included when using the driver.
flashm16c.h	This is the include file in the flash memory driver for the M16C type dependent
	part.
flashdrvdev_ew0.c	This is the EW0 mode flash memory driver file.
depend_m16c.c	This is the source of the flash memory driver for the M16C type dependent part.
ncrt0_EW0.a30	This is a C language initialization file.
	It is an upgraded version from the standard file (ncrt0.a30) with the RAM transfer
	processing at startup added.
sect30_EW0.inc	This is a C language section file.
	It has had a new program section that runs in the RAM added from the earlier
	version.
sfr26.h	These are include files for the M16C/26, 26A, 28 and 29. Please be sure to obtain the
sfr26a.h	latest file.
sfr28.h	
sfr29.h	
main_m16c.c	This file contains a sample program usage example.
M16C_EW0.tmk	This is the Makefile. (Specify make -f M16C_EW0.tmk to compile it.)

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4.2 Program Operation

This section explains operation of the sample program as flash memory driver.

The driver is always used when reading or writing to the flash memory, as well as when erasing the flash memory.

During read or write, the flash memory cannot be accessed for data readout (fetch or read).

The driver is assumed to be run in the RAM.

A sequence flow of the driver during auto erase is shown below.

4.2.1 Auto Program and Auto Erase Operations

The following shows an example driver operation using auto program and auto erase APIs.

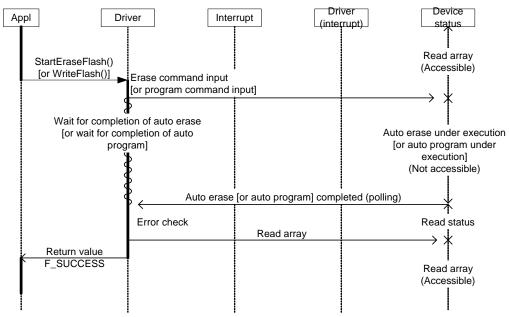


Figure 4-1. Operation of Auto Program and Auto Erase APIs -1

The auto program and the auto erase APIs return F_SUCCESS when the respective operations are successfully completed.

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4.2.2 Erase Suspend Processing

The SuspendErase() function suspends the erase processing being executed by StartEraseFlash() or RestartEraseFlash(). The operation sequence is shown below.

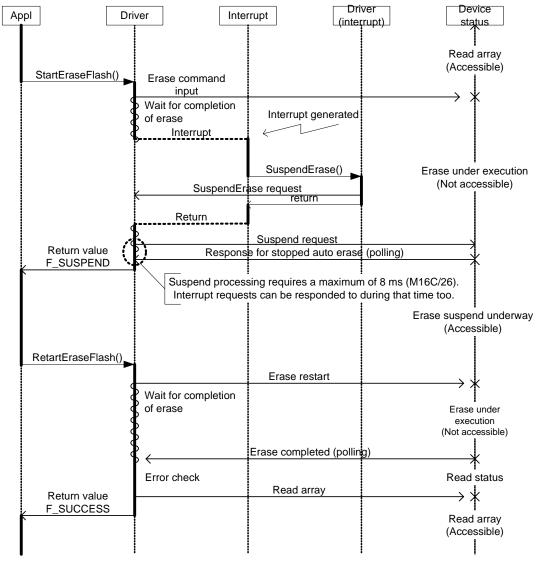


Figure 4-2. Erase Suspend Processing Sequence Flow -1

Called in an interrupt, SuspendErase() only issues a request to the driver, and does not perform any operation on the flash memory. The flash memory cannot be accessed for read during an interrupt. When a suspend request is issued, a finite time of up to 8 ms is required (for the M16C/26) until auto erase of the flash memory stops.

For details on how to read data from the flash memory during an interrupt, refer to Section 4.2.3, "Flash Memory Read during Interrupt Processing."

main Driver Explanation (interrupt) (timer) Suspend request Requested Interrupt generate --- Not request Calling SuspendErase() Interrupt during other than erase does Read array SuspendErase() not cause any action to take return Return StartEraseFlash(Erase command input Wait for completion Interrupt generate If SuspendErase request is of erase Interrupt issued in an interrupt, wait for Erase under execution dropped. completion of erase is SuspendErase() uspendErase reques (Not accessible) return Return Suspend request Return value Response for stopped auto erase (polling) The SuspendErase request F_SUSPEND issued during suspend is Interrupt generated stored in memory. (However, Interrupt stored only once no matter SuspendErase() how many times a request is spendErase reques issued, because no count return functions are available.) Return Erase is suspended immediately after it started RestartEraseFlash because a suspend request Erase command input already exists. Return value Suspend request F_SUSPEND for stopped auto era-(polling) Erase suspend underway Interrupt generated (Accessible) Interrupt SuspendErase() SuspendErase reques Return The suspend request is cleared temporarily before restarting. ResumErase() return RestartEraseFlash Erase command input Wait for completion Erase under execution of erase (Not accessible) Erase completed (pollin Error check Read status Read array Return value

The request from SuspendErase() processing holds the currently erase-suspended call too. ResumeErase() may be used to avoid it. A sequence is shown below.

Figure 4-3. Erase Suspend Processing Sequence Flow -2

Read array

(Accessible)

When erase is completed,

process returns with F SUCCESS.

Although the erase interface consists of synchronous functions, use of the SuspendErase() function allows for return from the erase interface.

As in Figure 4-3, "Erase Suspend Processing Sequence Flow -2," SuspendErase() processing may be periodically invoked using a timer in order to prevent the CPU from being occupied by StartFlashErase() or RestartFlashErase().

F_SUCCESS

4.2.3 Flash Memory Read during Interrupt Processing

Use the SuspendFlash() function to read data from the flash memory in an interrupt process during auto erase or auto program. Use ResumFlash() to restart auto erase after reading data from the flash memory.

The operation sequence is shown below.

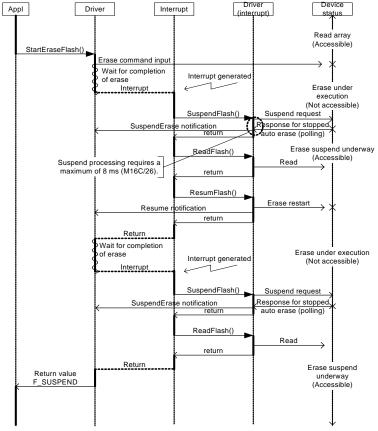


Figure 4-4. Flash Memory Read during Interrupt Processing (Auto Erase)

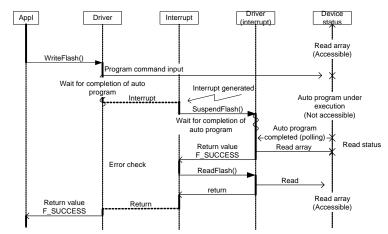


Figure 4-5. Flash Memory Read during Interrupt Processing (Auto Program)

No problems may be incurred by executing SuspendFlash() during other than auto program or auto erase.

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4.3 Software Interface

The sample program interface is described below.

Table 4-3. StartEraseFlash()

Outline	Erases the device.		
Declaration	FlashResul	t StartEraseFlash(F_ADR flashAddres	ss);
Include	flash_ew0d	rv.h	
Parameter		Meaning	Remark
F_ADR flashAddress		Highest address of the flash memory to be erased (even address)	
Return value		Meaning	Value
FlashResult		Error code	F_SUCCESS Successfully executed Other Error code See Table 4-13

Description

This function erases the flash memory (all 0xFF).

If SuspendErase() or SuspendFlash() is called in an interrupt process during erase and the interrupt processing is completed, this function is terminated in the middle, with the error code F_SUSPEND returned. In this case, RestartEraseFlash() described next should be called to resume suspended erase and complete it.

Error code

F_SUCCESSSuccessfully executed

Other Error code

See Table 4-13

Remark

If an error occurs (responded with error from the flash memory device), no retry operation is attempted.

If an error occurs, therefore, the erase operation should be retried a number of times as specified in the manual.

This function cannot be used in an interrupt.

Interrupts are controlled using the I flag internally. If interrupts need to be disabled in order to use this function, disable interrupts in the IPL.

Table 4-4. RestartEraseFlash()

Outline	Resumes device erase.			
Declaration	FlashResul	FlashResult RestartEraseFlash(void);		
Include	flash_ew0d	rv.h		
Parameter		Meaning	Remark	
None				
Return value		Meaning	Value	
FlashResult		Error code	F_SUCCESS Successfully executed Other Error code See Table 4-13	

Description

This function resumes erase of the flash memory (all 0xFF).

If StartEraseFlash() or RestartEraseFlash() returns with the error code F_SUSPEND (erase suspended), this function is called in order to resume suspended erase. When erase is completed after being resumed, F_SUCCESS is flagged. As for StartEraseFlash(), the erase operation resumed by this function can be suspended again by SuspendErase() or SuspendFlash().

Error code

F_SUCCESSSuccessfully executed

Other Error code

See Table 4-13

Remark

If an error occurs (responded with error from the flash memory device), no retry operation is attempted.

If an error occurs, therefore, the erase operation should be retried a number of times as specified in the manual.

This function cannot be used in an interrupt.

Interrupts are controlled using the I flag internally. If interrupts need to be disabled in order to use this function, disable interrupts in the IPL.

Table 4-5. WriteFlash()

Outline	Writes data	Writes data to the flash memory.		
Declaration	FlashResult WriteFlash(F_ADR flashAddress,			
		const void * buffer,		
		unsigned short size);		
Include	flash_ew0d	rv.h		
Parameter		Meaning	Remark	
F_ADR flashAd	ldress,	Beginning address of the area to	Because data is written in 2-	
		which data is to be written	byte units, specify an even	
			address.	
const void * buffer		Beginning address of the data to be written		
unsigned short size		The data size to be written	Be sure to specify in 2-byte	
			units.	
Return value		Meaning	Value	
FlashResult		Error code	F_SUCCESSSuccessfully	
			executed	
			Other Error code	
			See Table 4-13	
Description				

Description

This function writes data to the flash memory. Since data is written to the flash memory in 2-byte units, an even address must be specified for flashAddress and an multiple of 2 bytes must be specified for size.

An error is assumed unless the conditions are met.

Error code

F_SUCCESSSuccessfully executed

Other Error code

See Table 4-13

Remark

A write alignment error or write size error can be deleted by commenting out #define ENABLE_FLASH_ERR_CHECK. In this case, if a parameter error (2-byte data size check or alignment) occurs, the program behavior is undefined.

This function cannot be used in an interrupt.

Interrupts are controlled using the I flag internally. If interrupts need to be disabled in order to use this function, disable interrupts in the IPL.

Table 4-6. ReadFlash()

Outline	Reads data from the flash memory.			
Declaration	FlashResult ReadFlash(F_ADR flashAddress,			
		void * buffer,		
		unsigned short size);		
Include	flash_ew0d	rv.h		
Parameter		Meaning	Remark	
F_ADR flashAd	ldress	Beginning address of the read data		
void * buffer		Address into which data is read		
unsigned short	size	The data size to be written		
Return value		Meaning	Value	
FlashResult		Error code	F_SUCCESSSuccessfully	
			executed	
			Other Error code	
			See Table 4-13	
Description				
This function re	eads data fro	om the flash memory.		
Error code				
F_SUCCESSSi	F_SUCCESSSuccessfully executed			
	Other Error code			
See Table 4-13				
Remark	Remark			

Table 4-7. UnlockBlockFlash()

Outline	Unlocks flash memory blocks to lift write protect.			
Declaration	void UnlockBlockFlash(enum FlashBlock blockNumber);			
Include	flash_ew0d	rv.h		
Parameter		Meaning	Remark	
enum FlashBlo blockNumber	ck	Level of write protect to be lifted	When F_ALLBLOCK, all blocks are removed of write protect	
Return value		Meaning	Value	
None				
Description	Description			
This function unlocks flash memory blocks to lift write protect. F_BLOCK_2 to F_BLOCK_5: Blocks 2, 3, 4, 5, A and B are write enabled. (M16C/26A, 28 and 29) F_BLOCK_0 to F_BLOCK_1: Blocks 0, 1, 2, 3, 4, 5, A and B are write enabled.				
Error code	Error code			
None				
Remark	Remark			

Table 4-8. LockBlockFlash()

Outline	Locks flash memory blocks to write protect.		
Declaration	void LockBlockFlash(enum FlashBlock blockNumber);		
Include	flash_ew0d	rv.h	
Parameter		Meaning	Remark
enum FlashBlo blockNumber	ck	Level be write protected	When F_ALLBLOCK, all blocks are write protected
Return value		Meaning	Value
None			
Description			
F_BLOCK_2 to	This function locks flash memory blocks to write protect. F_BLOCK_2 to F_BLOCK_5: Blocks 0, 1, 2, 3, 4 and 5 are write enabled. F_BLOCK_0 to F_BLOCK_1: Blocks 0 and 1 are write protected.		
Error code None Remark			
Itemark			

Table 4-9. SuspendErase()

Outline	Issues a request to suspend wait for completion of erase		
Declaration	void SuspendErase(void);		
Include	flash_ew0d	rv.h	
Parameter		Meaning	Remark
None			
Return value		Meaning	Value
None			
Description			
		est to suspend processing while comple	
		${ m tEraseFlash}0$ is being waited for. The	content of processing varies
		nory status, as follows:	
During progr	_	: No operation performed	
_	During erase : A request to suspend wait for completion of erase is issued.		
_	During normal : No operation performed		
	During erase suspend : A request to suspend wait for completion of erase is issued.		
	If this function is called after calling the StartEraseFlash() function, StartEraseFlash() suspends		
erase and retur	ns with F_S	USPEND. Thereafter, erase is restarte	ed by RestartEraseFlash(). (In
this case, erase may be suspended again by SuspendErase().)			
Error code			
None			
Remark			

Table 4-10. ResumErase()

Outline	Cancels a request to suspend wait for completion of erase			
Declaration	void ResumErase(void);			
Include	flash_ew0d	lrv.h		
Parameter		Meaning		Remark
None				
Return value		Meaning		Value
None				
Description				
This function d	This function drops the request to suspend erase issued by SuspendErase().			ndErase().
If no requests of	If no requests occur, no operation is performed.			
Error code	Error code			
None				
Remark				
If this function is called after calling SuspendErase(), the request to suspend erase issued by				
SuspendErase() is dropped. However, this does not apply if this function is called after				
SuspendErase	SuspendErase() has once been accepted.			

Table 4-11. SuspendFlash()

Outline	Checks whether the flash memory can be accessed for read during erase or		
	program.		
Declaration	FlashResult SuspendFlash(void);		
Include	flash_ew0drv.h		
Parameter		Meaning	Remark
None			
Return value		Meaning	Value
FlashStatus		Flash memory status	
Description			
Used for interrupts only.			
This function checks whether the flash memory can be accessed for read while it is being erased. It			
is used for the purpose of inspection when the flash memory needs to be accessed for read in an			
interrupt sequence. The content of processing varies depending on the flash memory status, as			
follows:			
During programming		: Completion of programming is waited (software loop).	
During erase		: A suspend command is issued and completion of suspend or	
programming is waited (software loop).			
During normal		: No operation performed	
During erase suspend		: No operation performed	
Error code			
None			
Remark			

Table. 4-12 ResumFlash()

Outline	Restores from suspend state					
Declaration	FlashResult ResumFlash(void);					
Include	flash_ew0drv.h					
Parameter		Meaning	Remark			
None						
Return value		Meaning	Value			
FlashStatus		Flash memory status				
Description						
Used for interrupts only.						
This function restores the driver from a suspend state and let it start erasing the flash memory.						
This function is used in pairs with SuspendFlash().						
If this function is called during other than suspend, no operation is performed.						
Error code						
None						
Remark						

Table 4-13. Error Code (enum FlashResult)

Name	Value	Meaning		
F_SUCCESS	0	Successfully executed.		
F_WRITE_ERROR	1	Write error. A write error was notified from the flash		
		memory.		
F_ERASE_ERROR	2	Erase error.		
F_CMD_SEQUENCE_ERR	3	Sequence error. A sequence error was notified from the		
OR		flash memory.		
F_WRITE_ADDRESS_ERR	4	Write address alignment error (2 bytes aligned)		
OR				
F_WRITE_SIZE_ERROR	5	Invalid write size error (written in 2-byte units)		
F_DEVICE_BUSY	6	Device busy (read during programming or erase)		
F_SUSPEND	7	Suspended by a suspend request in the middle of		
		programming		
F_RESUM_ERROR	8	Called by ResumFlash() when not suspended		
F_RESET_OCCURRED	9	When the flash memory is reset		

4.4 Customization

The sample program requires partial setup that needs to be made for each system.

The following describes how to customize the sample program to make it suitable for each system.

4.4.1 Customizing CPU Clock Settings

In CPU rewrite mode, the CPU clock settings are subject to limitations.

To meet the conditions, customize the processing in the functions listed below.

In the sample program, the CPU clock settings are created assuming M16C/28 Xin = 20 MHz.

Table 4-14. Functions That Need to Be Customized

Function name	Description		
void SlowMCU(ProcessorMode * save);	Corrects the CPU clock settings to overcome the limitations		
	and saves the settings prior to correction in save.		
void RestoreMCU(ProcessorMode * save);	Restores the save data as CPU clock settings.		

For details about clock limitations, refer to the contents described in Section 3.5.1.

4.4.2 Customizing Operation of the Driver Software

Use flashdevconf.h to customize the driver software.

Table 4-15. Definition of Sample Program Options

Setup content	Define name	Default	Contents to be set or description
CPU series setting	M16C_SERIES	M16C_SERIES	Add a M16C type dependent part to
			the source.
CPU group setting	M16C_26	M16C_28	Set a CPU group.
	M16C_26A		Include the header provided for each
	M16C_28		type. Add a type dependent part of lock
	M16C_29		bit settings.
Programming mode	FLASH_MODE_EW0	FLASH_MODE_	Select the programming mode used.
setting		EW0	
Watchdog timer	ENABLE_WATCHDOG_	Unspecified	Specify whether or not to clear the
clear	RESET		watchdog timer while waiting for
			completion of auto erase or auto
			program. Normally, do this in the main
			processing of the user program rather
			than using this processing.
Address error check	ENABLE_FLASH_ERR_	ENABLE_FLAS	Check address alignment and 2-byte
specification	CHECK	H_ERR_CHECK	unit programming.
Definition for use of	USE_SUSPEND_FLAS	Unspecified	Define this when the SuspendFlash()
flash memory	H_FUNCTION		function is to be used. Normally, use
suspend function			the SuspendFlash() function.
Definition of flash	F_ADR_SIZE	Far	Specify the definition of the write
memory address			pointer that indicates the flash
			memory location to which to write. If
			only the data area needs to be written
			to, this can be defined as near.

5. Using the Sample Program

An example method for using the sample program is shown in the main of main_m16c.c. For details on how to use, refer to the main_m16c.c file.

The following shows specifications of the main processing.

- Operates with M16C/28 Xin = 20 MHz.
- · The main loop executed every 20 ms is created by timer A interrupt processing.
- · Block B is erased every 1 s.
- Erase is suspended every 20 ms, with control returned to the main loop. This processing is performed in timer A interrupt processing.
- After completion of erase, data is written to the flash memory every 32 bytes beginning with 0F00016 and the written data is read out.

5.1 Source Code

5.1.1 flashdevconf.h

```
/*
   FILE NAME : flashdevconf.h
/*
   Ver : 1.00
    CPU
            : M16C/Tiny R8C/Tiny
   FUNCTION : Flash erase/read/write driver.
            by EWO or EW1 mode operation
/*----
/* Copyright(C)2004, Renesas Technology Corp.
/* Copyright(C)2004, Renesas Solutions Corp.
/* All rights reserved.
// $Id: flashdevconf.h,v 1.9 2004/07/02 06:12:02 kato Exp $
#ifndef ___FLASHDEVCONF_H__
#define ___FLASHDEVCONF_H__
//#define DEBUG
//#define R8C_SERIES
//#define R8C_10
//#define R8C_11
//#define R8C_12
//#define R8C_13
#define M16C_SERIES
#define M16 26
//#define M16_26A
//#define M16_28
//#define M16_29
#define FLASH MODE EW0
//#define FLASH_MODE_EW1
// Watch Dog Reset Enable
//#define ENABLE_WATCHDOG_RESET
//#define ENABLE_FLASH_ERR_CHECK
// USE SuspendFlash function
#define USE_SUSPEND_FLASH_FUNCTION
#if defined(M16C_SERIES)
#define F_ADR_SIZE far
#elif defined(R8C_SERIES)
#define F_ADR_SIZE
#undef ENABLE_FLASH_ERR_CHECK
#else
#error "Please choose either R8C_SERIES\ or M16C_SERIES\."
#if (!defined(FLASH_MODE_EW0) && !defined(FLASH_MODE_EW1))
#error "Please choose FLASH_MODE_EWO , FLASH_MODE_EWO or both. "
#endif
#endif /* #ifndef __FLASHDEVCONF_H__ */
```

5.1.2 flashdevdrv.h

```
FILE NAME : flashdevdrv.h
/*
     Ver : 1.00
      CPU
                 : M16C/26
/*
      FUNCTION : Flash erase/read/write driver.
                  by EWO or EW1 mode operation
/*----
/* Copyright(C)2004, Renesas Technology Corp.
/* Copyright(C)2004, Renesas Solutions Corp.
                                                                             * /
/* All rights reserved.
// $Id: flashdevdrv.h,v 1.5 2004/07/22 04:06:41 ikari Exp $
#include "flashdevconf.h"
#ifndef ___FLASHDEVDRV_H__
#define ___FLASHDEVDRV_H__
#if (defined(FLASH_MODE_EW0) && !defined(FLASH_MODE_EW1))
#define WriteFlash(a,b,c) WriteFlashEW0(a,b,c)
#define ReadFlash(a,b,c) ReadFlashEW0(a,b,c)
#define StartEraseFlash(a) StartEraseFlashEW0(a)
#define RestartEraseFlash() RestartEraseFlashEW0()
#define SuspendErase() SuspendEraseEW0()
#define ResumErase()
#define ResumErase() ResumEraseEW0()
#define GetFlashStatus() GetFlashStatusEW0()
#endif /* #if (defined(FLASH_MODE_EW0) && !defined(FLASH_MODE_EW1)) */
#if (!defined(FLASH_MODE_EW0) && defined(FLASH_MODE_EW1))
#define WriteFlash(a,b,c) WriteFlashEW1(a,b,c)
#define ReadFlash(a,b,c) ReadFlashEW1(a,b,c)
#define StartEraseFlash(a) StartEraseFlashEW1(a)
#define RestartEraseFlash() RestartEraseFlashEW1()
#define SuspendFrase() SuspendFraseFW1()
#define SuspendErase() SuspendEraseEW1()
#define ResumErase() ResumEraseEW1()
#define GetFlashStatus() GetFlashStatusEW1
                                   GetFlashStatusEW1()
#endif /* #if (!defined(FLASH_MODE_EW0) && defined(FLASH_MODE_EW1)) */
/*----*/
/*! The address definition of the flash memory */
typedef void F_ADR_SIZE * F_ADR;
/*! Error code */
typedef enum FlashResult{
    F_SUCCESS, /*! Success */
F_WRITE_ERROR, /*! Program error (from the flash device) */
F_ERASE_ERROR, /*! Block erase error (from the Flash device) */
F_CMD_SEQUENCE_ERROR, /*! Command sequence error(from the Flash device) */
    F_WRITE_ADDRESS_ERROR, /*! The address alignment error of the argument */
    F_WRITE_SIZE_ERROR, /*! The size error of the argument
    F_DEVICE_BUSY,
                              /*! When a Read/Programing/Erasing requirement */
                         /* in Programing/Erasing occurs.
/*! Suspend requirement acceptance.
/*! When Suspend isn't being done with
                                                                                     * /
    F SUSPEND,
    F_RESUM_ERROR,
                              /* ResumFlash(), call
    F_RESET_OCCURRED,
                              /*! Resetting was done during the
                               /* Programing/Erasing as to the call.
} FlashResult;
```

```
/*-----/
/*!
* Initialize flash device.
void FlashInitialize(void);
* Device resetting.
* /
void FlashReset(void);
* Erase flash memory in the EWO mode.
* @param flashAddress
                             [in] physical address of the head of
                                  the block on flash.
* @return Success or Error code.
* @retval F_SUCCESS
                              Success
* @retval F_ERASE_ERROR
                              Block erase error (from the Flash device)
* @retval F_CMD_SEQUENCE_ERROR Command sequence error(from the Flash device)
 * @retval F_WRITE_ADDRESS_ERROR The address alignment error of the argument.
* @retval F_DEVICE_BUSY
                             When a Read/Programing/Erasing requirement
                              in Programing/Erasing occurs.
* @retval F_SUSPEND
                              Suspend requirement acceptance.
FlashResult StartEraseFlashEWO(F_ADR flashAddress);
/*----*/
\mbox{\scriptsize \star} Erase flash memory in the EW1 mode.
* @param flashAddress [in] physical address of the head of
                                 the block on flash.
* @return Success or Error code.
* @retval F_SUCCESS
                             Success
* @retval F_ERASE_ERROR
                             Block erase error (from the Flash device)
* @retval F_CMD_SEQUENCE_ERROR
                             Command sequence error(from the Flash device)
^{\star} @retval F_WRITE_ADDRESS_ERROR \,\,\,\,\, The address alignment error of the argument.
* @retval F_DEVICE_BUSY
                              When a Read/Programing/Erasing requirement
                              in Programing/Erasing occurs.
* @retval F_SUSPEND
                              Suspend requirement acceptance.
 * /
FlashResult StartEraseFlashEW1(F_ADR flashAddress);
/*!
* Restart to erase a block of the flash memory in the EWO mode.
* @return Success or Error code.
* @retval F SUCCESS
                              Success
* @retval F_ERASE_ERROR
                             Block erase error (from the Flash device)
* @retval F_CMD_SEQUENCE_ERROR
                             Command sequence error(from the Flash device)
^{\star} @retval F_WRITE_ADDRESS_ERROR \,\,\,\,\, The address alignment error of the argument.
* @retval F_DEVICE_BUSY
                              When a Read/Programing/Erasing requirement
                              in Programing/Erasing occurs.
 * @retval F_SUSPEND
                              Suspend requirement acceptance.
FlashResult RestartEraseFlashEW0(void);
/*----*/
* Restart to erase a block of the flash memory in the EW1 mode.
 * @return Success or Error code.
 * @retval F_SUCCESS
                              Success
* @retval F_ERASE_ERROR
                             Block erase error (from the Flash device)
* @retval F_CMD_SEQUENCE_ERROR
                             Command sequence error(from the Flash device)
 * @retval F_WRITE_ADDRESS_ERROR The address alignment error of the argument.
 * @retval F_DEVICE_BUSY
                              When a Read/Programing/Erasing requirement
```

```
in Programing/Erasing occurs.
 * @retval F_SUSPEND
                                Suspend requirement acceptance.
FlashResult RestartEraseFlashEW1(void);
\mbox{\ensuremath{^{\star}}} Write data to flash memory in the EWO mode.
* @param flashAddress
                               [in] physical address on flash to begin write
* @param buffer
                               [in] address in buffer to write from
* @param size
                               [in] number of byte to write.
* @return Success or Error code.
* @retval F_SUCCESS
                               Success
 * @retval F_WRITE_ERROR
                               Program error (from the flash device)
 * @retval F_CMD_SEQUENCE_ERROR Command sequence error(from the Flash device)
* @retval F_WRITE_ADDRESS_ERROR The address alignment error of the argument.
* @retval F_WRITE_SIZE_ERROR, The size error of the argument
* @retval F_DEVICE_BUSY
                               When a Read/Programing/Erasing requirement
                               in Programing/Erasing occurs.
FlashResult WriteFlashEW0(F_ADR flashAddress,
                       const void * buffer,
                       unsigned short size);
* Write data to flash memory in the EW1 mode.
 * @param flashAddress
                               [in] physical address on flash to begin write.
* @param buffer
                               [in] address in buffer to write from.
* @param size
                               [in] number of byte to write.
* @return Success or Error code.
* @retval F_SUCCESS
                               Success
 * @retval F_WRITE_ERROR
                               Program error (from the flash device)
 * @retval F_CMD_SEQUENCE_ERROR
                               Command sequence error(from the Flash device)
 * @retval F_WRITE_ADDRESS_ERROR The address alignment error of the argument.
* @retval F_WRITE_SIZE_ERROR,
                              The size error of the argument
* @retval F_DEVICE_BUSY
                               When a Read/Programing/Erasing requirement
                               in Programing/Erasing occurs.
* /
FlashResult WriteFlashEW1(F_ADR flashAddress,
                       const void * buffer,
                       unsigned short size);
/*----*/
/*!
* Read data from flash memory for the EW1 mode.
* @param flashAddress
                               [in] physical address on flash to begin read.
 * @param buffer
                               [out] address in buffer to read to.
                               [in] number of byte to read.
* @param size
* @return Success or Error code.
* @retval F_SUCCESS
                               Success
* @retval F_DEVICE_BUSY
                               When a Read/Programing/Erasing requirement
                               in Programing/Erasing occurs.
FlashResult ReadFlashEWO(F_ADR flashAddress,
                      void * buffer,
                      unsigned short size);
* Read data from flash memory for the EW1 mode.
 * @param flashAddress
                               [in] physical address on flash to begin read.
 * @param buffer
                               [out] address in buffer to read to.
 * @param size
                               [in] number of byte to read.
 * @return Success or Error code.
 * @retval F_SUCCESS
                               Success
 * @retval F_DEVICE_BUSY
                               When a Read/Programing/Erasing requirement
```

```
in Programing/Erasing occurs.
* /
FlashResult ReadFlashEW1(F_ADR flashAddress,
                void * buffer,
                unsigned short size);
/*! Block number */
enum FlashBlock{
  F_BLOCK_0,
  F_BLOCK_1,
  F_BLOCK_2,
  F_BLOCK_3,
  F_BLOCK_4,
  F BLOCK 5.
  F_ALLBLOCK = -1,
  F_BLOCK_A = -2,
  F_BLOCK_B = -3,
};
/*----*/
/*!
* Disable write protect.
* @param blockNumber
                       [in] The block number to protect it.
void UnlockBlockFlash(enum FlashBlock blockNumber);
/*-----*/
* Enable write protect.
* @param blockNumber
                        [in] The block number to unprotect it.
* /
void LockBlockFlash(enum FlashBlock blockNumber);
/ * !
\ ^{\star} Send the suspension request of a flash memory in the EWO mode.
void SuspendEraseEW0(void);
/*----*/
/*!
* Send the suspension request of a flash memory in the EW1 mode.
void SuspendEraseEW1(void);
/*----*/
/*!
* Clear the suspension request of a flash memory in the EWO mode.
void ResumEraseEW0(void);
\mbox{\scriptsize \star} Clear the suspension request of a flash memory in the EWO mode.
void ResumEraseEW1(void);
/*! Status of flash memory or this driver. */
typedef enum FlashStatus{
  FLASH_READY,
                     /*! ready
                                                    * /
  FLASH_WRITE,
                     /*! programing
  FLASH_ERASE,
                     /*! erasing
  FLASH_SUSPEND,
                     /*! suspend erasing
  FLASH_INT_SUSPEND,
                     /*! suspend erasing during the interruption */
```

```
\mbox{\scriptsize \star} Get flash memory status for the EWO mode.
FlashStatus GetFlashStatusEW0(void);
/*-----/
/*!
* Get flash memory status for the EW1 mode.
FlashStatus GetFlashStatusEW1(void);
#ifdef FLASH_MODE_EW0
/*-----*/
/*!
* Suspend at interrupt.
FlashResult SuspendFlashEWO(void);
/*----*/
^{\star} This function resumes the erasure processing suspended by SuspendFlashEWO().
FlashResult ResumFlashEWO(void);
#endif
#endif /* #ifndef __FLASHDEVDRV_H__ */
```

5.1.3 flashm16c.h

```
/*
   FILE NAME : flashm16c.h
/*
   Ver : 1.00
/*
   CPII
            : M16C
   FUNCTION : Flash erase/read/write driver.
             by EWO or EW1 mode operation
/*-----
/* Copyright(C)2004, Renesas Technology Corp.
/* Copyright(C)2004, Renesas Solutions Corp.
/* All rights reserved.
// $Id: flashm16c.h,v 1.4 2004/06/30 02:28:41 nagayoshi Exp $
#include "flashdevconf.h"
     defined( M16_26 )
#if
#include "sfr26.h"
#elif defined( M16_26A )
#include "sfr26a.h"
#elif defined( M16_28 )
#include "sfr28.h"
#elif defined( M16_29 )
#include "sfr29.h"
#else
#error "This cpu type not support."
#endif
#ifndef __FLASHM16C_H_
#define __FLASHM16C_H__
//typedef volatile unsigned short F_ADR_SIZE * DEPEND_F_ADR;
typedef volatile unsigned short DEPEND_FSIZE;
#define FLASH_READARRAY_CMD
                                ((unsigned short)0xff)
#define FLASH_STSREGS_CMD
                                ((unsigned short)0x70)
                                ((unsigned short)0x50)
#define FLASH_CLEAR_STSREGS_CMD
#define FLASH_PRG_CMD
                                 ((unsigned short)0x40)
#define FLASH_BLOCK_ERASE_1_CMD
                                 ((unsigned short)0x20)
#define FLASH_BLOCK_ERASE_2_CMD
                                 ((unsigned short)0xd0)
#define _FLASH_E_EW() {\
  fmr01 = 0; \
   asm("");
   fmr01 = 1;
   asm("");
}
#define _FLASH_DIS_EW() {\
  fmr01 = 0; \
}
#define _FLASH_E_SUSPEND() {\
  asm("");
   fmr40 = 1; \
   asm("");
}
#define _FLASH_SUSPEND_ERASE() {\
   fmr41 = 1;
#define _FLASH_RESUME_ERASE() {\
```

```
fmr41 = 0; \
}
#define _FLASH_RESUME_ERASE_EW1(a) {\
   fmr41 = a; \
#define _FLASH_EW1_MODE() {\
   fmr11 = 0;
   fmr11 = 1;\
}
#define _CLEAR_WATCHDOG() {\
   wdts = 0x7fff;
#define _FLASH_BUSY() (fmr00 == 0)
#define _FLASH_DEVICE_INIT() {\
   fmr17 = 1;
                  /* Unlock CM0, CM1, PM1 */\
   prcr = 0x3;
                /* enable flash data block (4KB Virtual EEPROM) access */ \setminus
  pm10 = 1;
                 /* Lock the System Clock Control Register */ \
   prcr = 0;
}
#define ERASE_ERR 0x40
#define PRGRAM_ERR 0x80
#define FMR07_06 (PRGRAM_ERR | ERASE_ERR)
#define _FLASH_GET_STAT_FLG() (fmr0 & FMR07_06)
#define DEBUG_OUT_ERASE_START 0x04 /* xxxx100 */
                                  /* xxxx010 */
#define DEBUG_OUT_SUSPEND 0x02
#define DEBUG_OUT_READY 0x07
                                    /* xxxx111 */
#define DEBUG_OUT_WAIT_ERASE 0xFF
                                    /* not use */
//#define DEBUG_M16C
#ifdef DEBUG_M16C
#define DEBUG_OUT(a) {\
   }
#else
#define DEBUG_OUT(a)
#endif /* #ifdef DEBUG_M16C */
struct LockBitStatus{
   unsigned char s_fmr16:1;
   unsigned char s_fmr02:1;
};
/*! for SlowMCU/RestoreMCU */
#define USE CLOCKGEAR
typedef struct ProcessorMode
    unsigned char p_pm1;
    unsigned char p_cm0;
    unsigned char p_cml;
} ProcessorMode;
void SlowMCU(ProcessorMode * save);
void RestoreMCU(ProcessorMode * save);
#endif /* #ifndef __FLASHM16C_H__ */
```

5.1.4 flashdrvdev ew0.c

```
FILE NAME : flashdrvdev_ew0.c
    Ver : 1.00
CPU : R8C M16C/26,26A,28,29
/*
   FUNCTION : Flash low level (erase/read/write) driver.
             by EWO mode operation
/*----*/
/* Copyright(C)2004, Renesas Technology Corp.
/* Copyright(C)2004, Renesas Solutions Corp.
/* All rights reserved.
/*
// $Id: flashdrvdev_ew0.c,v 1.11 2004/07/21 09:04:39 kato Exp $
* /
#include <string.h>
#include "flashdevdrv.h"
#if defined(M16C_SERIES)
#include "flashm16c.h"
#elif defined(R8C_SERIES)
#include "flashr8c.h"
#endif
#ifdef FLASH_MODE_EW0
/*! Flash status
enum FlashStatus stat = FLASH_READY;
/*! Flash status
struct {
   unsigned char suspReq:1;
   unsigned char rstOccerred:1;
f_flags = {0,0};
#define suspendReq f_flags.suspReq
#define resetOccerrd f_flags.rstOccerred
/*! Command target address. */
DEPEND_FSIZE F_ADR_SIZE * com_adr;
/*=== Prototype =========*/
FlashResult EraseCheckInternal(void);
FlashResult FullStatusCheck(void);
void SetUpLockBit(void);
/* There functions are running on RAM.*/
void RestartFlashEraseRam(void);
void FlashEraseCommandRam(DEPEND_FSIZE F_ADR_SIZE * flashAddress);
void FlashWriteCommandRam(DEPEND_FSIZE F_ADR_SIZE * flashAddress ,
                    unsigned short data);
void WaitEraseCompleteRam(DEPEND_FSIZE F_ADR_SIZE * flashAddress);
void FlashSuspendRam(void);
/***********************************
         :FlashInitialize()
Name
         :Initialization of a flash memory.
Purpose
        :Result.
Returns
        :None.
Notice
*************************
void FlashInitialize(void)
   _FLASH_DEVICE_INIT();
   FlashReset();
}
```

```
:ReadFlashEW0()
Purpose
        :Read data from flash memory.
Arguments :
   [in] flashAddress physical add on flash to begin read
   [out] buf
                    address in buffer to read to
                   number of byte to read
   [in] size
Return
         :Result
         :None
Notice
*******************************
FlashResult ReadFlashEWO(F_ADR flashAddress,
                     void * buf,
                     unsigned short size)
{
   if(stat != FLASH_READY && stat != FLASH_SUSPEND)return F_DEVICE_BUSY;
   memcpy( buf , flashAddress , size);
   return F_SUCCESS;
}
:StartEraseFlashEW0()
Purpose :Start to erase 1 block of the flash memory.
Arguments :physical address of the head of the block on flash.
        :Result
Return
          :This function erase and return result only.
          This function does not perform retry at the time of error.
FlashResult StartEraseFlashEWO(F_ADR flashAddress)
   FlashResult ret;
#if defined(USE_CLOCKGEAR)
   ProcessorMode save_dat;
#endif
   DEPEND_FSIZE F_ADR_SIZE * adr = flashAddress;
#ifdef ENABLE_FLASH_ERR_CHECK
   if(0x01 & ((unsigned long)adr ))return F_WRITE_ADDRESS_ERROR;
#endif
   // disable interrupt.
   asm("FCLR I");
   if(stat != FLASH_READY){
      asm("FSET I");
      return F_DEVICE_BUSY;
   }
   asm("FSET I");
                   /* initialize request */
   suspendReq = 0;
   resetOccerrd = 0;  /* initialize reset_flags */
#if defined(USE_CLOCKGEAR)
   SlowMCU(&save_dat); // Must change main clock speed to meet flash
#endif
   asm("FCLR I");
   _FLASH_E_EW();
   asm("FSET I");
   asm("FCLR I");
   SetUpLockBit();
   asm("FSET I");
   asm("FCLR I");
   _FLASH_E_SUSPEND();
```



```
asm("FSET I");
   // Clear status register.
   asm("FCLR I");
   *adr = FLASH_CLEAR_STSREGS_CMD;
                             // Clear status register
   com_adr = adr;
   stat = FLASH_ERASE;
   // Flash command (Erase) entry.
   DEBUG_OUT(DEBUG_OUT_ERASE_START);
   FlashEraseCommandRam(adr); // I-flag is set in this function.
   ret = EraseCheckInternal();
   _FLASH_DIS_EW();
#if defined(USE_CLOCKGEAR)
                      // Restore clock back to original speed
  RestoreMCU(&save_dat);
#endif
  return ret;
}
:RestartEraseFlashEW0()
Purpose : Restart to erase 1 block of the flash memory.
Return
        :Result
       :This function erases flash memory with operating erase command.
         It does not perform retry at the time of error.
FlashResult RestartEraseFlashEW0(void)
  FlashResult ret;
#if defined(USE_CLOCKGEAR)
   ProcessorMode save_dat;
#endif
   asm("FCLR I");
   if(stat != FLASH_SUSPEND){
     asm("FSET I");
     return F_DEVICE_BUSY;
   asm("FSET I");
#if defined(USE_CLOCKGEAR)
   SlowMCU(&save_dat);
                      // Must change main clock speed to meet flash
#endif
   asm("FCLR I");
   _FLASH_E_EW();
   asm("FSET I");
   asm("FCLR I");
   SetUpLockBit();
   asm("FSET I");
   DEBUG_OUT(DEBUG_OUT_ERASE_START);
   asm("FCLR I");
   stat = FLASH_ERASE;
```

```
ret = EraseCheckInternal();
   _FLASH_DIS_EW();
#if defined(USE_CLOCKGEAR)
   RestoreMCU(&save_dat);
                       // Restore clock back to original speed
#endif
   return ret;
:EraseCheckInternal()
         :The eraseed result is judged.
        :Result.
FlashResult EraseCheckInternal(void)
   FlashResult ret;
   if(_FLASH_BUSY()){
      DEBUG_OUT(DEBUG_OUT_SUSPEND);
      stat = FLASH_SUSPEND;
      ret = F_SUSPEND;
   }
   else{
      DEBUG_OUT(DEBUG_OUT_READY);
                                // Erasing error?
      ret = FullStatusCheck();
      asm("FCLR I");
      _FLASH_RESUME_ERASE();
                                // take the precaution of resumeing.
      stat = FLASH_READY;
      asm("FSET I");
   }
   return ret;
}
/************************************
     :WriteFlashEW0()
Purpose
        :Write data to flash memory.
Arguments
        :Address
   [in] flashAddress physical add on flash to begin write
             address in bull number of byte to write
   [in] buf
                   address in buffer to write from
   [in] size
        :Result
Return
        :This function writes flash memory with operating write command.
          It does not perform retry at the time of error.
************************
FlashResult WriteFlashEW0(F_ADR flashAddress,
                     const void * buffer,
                     unsigned short size)
#if defined(USE_CLOCKGEAR)
  ProcessorMode save_dat;
#endif
   FlashResult ret;
   DEPEND_FSIZE F_ADR_SIZE * adr = flashAddress;
   const DEPEND_FSIZE * buf = buffer;
#ifdef ENABLE_FLASH_ERR_CHECK
   if(0x01 & ((unsigned long)adr ))return F_WRITE_ADDRESS_ERROR;
   if(0x01 & size)return F_WRITE_SIZE_ERROR;
```

```
#endif
   // disable interrupt.
   asm("FCLR I");
   if(stat != FLASH_READY){
      asm("FSET I");
      return F_DEVICE_BUSY;
   }
   asm("FSET I");
   resetOccerrd = 0;  /* initialize reset_flags */
#if defined(USE_CLOCKGEAR)
   SlowMCU(&save_dat); // Must change main clock speed to meet flash
#endif
   asm("FCLR I");
   _FLASH_E_EW();
   asm("FSET I");
   asm("FCLR I");
   SetUpLockBit();
   asm("FSET I");
   ret = F_SUCCESS;
   while(size > 0) {
      asm("FCLR I");
      stat = FLASH_WRITE;
      * adr = FLASH_CLEAR_STSREGS_CMD; /* Clear status register
      FlashWriteCommandRam(adr , *buf); /* I-flag is set in this function. */
                                   /* Write error?
      ret = FullStatusCheck();
      stat = FLASH_READY;
      if(ret != F_SUCCESS) break;
      size -= sizeof(DEPEND_FSIZE);
                                    /* subract 2 from byte counter
                                    /* increase to next data index
      buf++;
      adr++;
                                     /* increase to next flash index
   }
   // disable interrupt.
   asm("FCLR I");
   _FLASH_DIS_EW();
#if defined(USE_CLOCKGEAR)
  #endif
                    // Write Pass
   return ret;
}
:FullStatusCheck()
        :Check the status of flash memory.
Purpose
Arguments : None
         :Result
FlashResult FullStatusCheck(void)
   unsigned char reg;
   reg = _FLASH_GET_STAT_FLG();
   if(resetOccerrd)return F_RESET_OCCURRED;
   if(reg == 0)return F_SUCCESS;
   if(reg == PRGRAM_ERR) return F_WRITE_ERROR;
   if(reg == ERASE_ERR) return F_ERASE_ERROR;
   return F_CMD_SEQUENCE_ERROR;
```



```
}
/*******************************
running on RAM
#pragma SECTION program program_ram
Name
        :SuspendEraseEW0()
      :Send the suspension request of a flash memory.
        :None
**************************
void SuspendEraseEW0(void)
  /* send event to wait roop */
  suspendReq = 1;
}
:ResumEraseEWO()
Purpose
        :This function clears suspension request.
        :None
Return
******************************
void ResumEraseEW0(void)
   /* send event to wait roop */
  suspendReq = 0;
Name
        :FlashReset()
Purpose
        :Reset flash memory.
Return
        :None
        :If you use "KD30 debugger", it is necessary to set a setup of
        "KD30 debugger" to "FreeRunMode."
******
              void FlashReset(void)
  unsigned char fmr01_reg;
  unsigned char cnt;
#if defined(USE_CLOCKGEAR)
  ProcessorMode save_dat;
                  // Must change main clock speed to meet flash
  SlowMCU(&save_dat);
#endif
   // disable interrupt.
   asm("FCLR I");
   fmr01\_reg = fmr01;
   _FLASH_E_EW();
  fmstp = 1;
// cnt = 1; while(cnt --);
   fmstp = 0;
  if(fmr01_reg == 0)_FLASH_DIS_EW();
  resetOccerrd = 1;
   /* Wait 10us
   * 1/10MHz = 100ns
   * DEC.B lcycle + JNE 2+2cycle = 5 cycle
   * 10us/100ns/5 = 20
   cnt = 20;while(-- cnt);
   asm("FSET I");
```

```
#if defined(USE_CLOCKGEAR)
  #endif
}
/***************************
        :FlashWriteCommandRam
Purpose :Operate write command on RAM and enable interrupt.
       :None
        :This functions on the RAM.
*******************
void FlashWriteCommandRam(DEPEND_FSIZE F_ADR_SIZE * flashAddress ,unsigned short data)
   *flashAddress = FLASH_PRG_CMD; // Send write command
  *flashAddress = data;
                              // Write next word of data
  asm("FSET I");
   while( _FLASH_BUSY() );
   *flashAddress = FLASH_READARRAY_CMD; // Read allay command
}
:FlashEraseCommandRam
        :Erase flash memory and enable interrupt.
Purpose
Return
        :None
      :None
:This functions on the RAM.
Notice
**************************
void FlashEraseCommandRam(DEPEND_FSIZE F_ADR_SIZE * flashAddress)
  *flashAddress = FLASH_BLOCK_ERASE_1_CMD; // Send erase command
*flashAddress = FLASH_BLOCK_ERASE_2_CMD; // Send erase confirm
                                    // Send erase confirm command
   asm("FSET I");
   WaitEraseCompleteRam(flashAddress);
}
:RestartFlashEraseRam()
        :Restart Erasing.
Purpose
       :None
      :None
:This functions on the RAM.
                   *************************************
void RestartFlashEraseRam(void)
  _FLASH_RESUME_ERASE();
   asm("FSET I");
  WaitEraseCompleteRam(com_adr);
  return ;
}
:WaitEraseCompleteRam
Name
        :Wait until complete or suspended.
         Flash memory will be set "Read Array" mode (you can read data on
        flash memory) , if this function return.
Return :None
Notice
        :This functions on the RAM.
void WaitEraseCompleteRam(DEPEND_FSIZE F_ADR_SIZE * flashAddress)
    DEBUG_OUT(DEBUG_OUT_WAIT_ERASE);
   while( _FLASH_BUSY() ) {
#ifdef ENABLE_WATCHDOG_RESET
     _CLEAR_WATCHDOG();
#endif
     if(suspendReq){
```

```
suspendReq = 0;
         FlashSuspendRam();
         /* Data on the flash memory can't be read if Read-Array Mode isn't
         taken when elimination is completed when a Suspend requirement is accepted. ^{*}/
         if( !_FLASH_BUSY() )break;
         return;
   *flashAddress = FLASH_READARRAY_CMD;// Read allay command
}
:WaitEraseCompleteRam
Purpose :Block erase command is suspended.
         Wait until suspended.
Return
       :None
        :This functions on the RAM.
Notice
void FlashSuspendRam(void)
   _FLASH_SUSPEND_ERASE();
   while(fmr46 != 1);
}
:SuspendFlashEW0()
        :Suspend at interrupt.
Purpose
        :Result.
Return
        :Don't use under multiplex interruption.
*******************************
#ifdef USE_SUSPEND_FLASH_FUNCTION
unsigned char susModeBackup = 0;
FlashResult SuspendFlashEW0(void)
   switch(stat){
   case FLASH_ERASE:
      DEBUG_OUT(DEBUG_OUT_SUSPEND);
      suspendReq = 1;
      stat = FLASH_INT_SUSPEND;
      susModeBackup = fmr4;
      FlashSuspendRam();
      if( !_FLASH_BUSY() )return F_SUCCESS;
      *com_adr = FLASH_READARRAY_CMD; /* Read allay command */
      return F_SUSPEND;
   case FLASH_WRITE:
      while( _FLASH_BUSY() );
      *com_adr = FLASH_READARRAY_CMD; /* Read allay command */
      break;
   default:
      break;
   return F_SUCCESS;
}
       :ResumFlashEW0(void)
Purpose :This function resumes the erasure processing suspended by SuspendFlashEWO().
        :None
Return
         :Don't use under multiplex interruption.
******************************
FlashResult ResumFlashEW0(void)
   if(stat == FLASH_INT_SUSPEND){
      DEBUG_OUT(DEBUG_OUT_ERASE_START);
      stat = FLASH_ERASE;
      fmr4 = (0x03 \& susModeBackup);
```



5.1.5 depend_m16c.c

```
/*
   FILE NAME : depend_m16c.c
/*
   Ver : 1.00
/*
           : M16C/26,26A,28,29
    CPII
   FUNCTION : Flash low level (erase/read/write) driver for M16C */
/*----*/
/* Copyright(C)2004, Renesas Technology Corp.
/* Copyright(C)2004, Renesas Solutions Corp.
/* All rights reserved.
// $Id: depend_m16c.c,v 1.2 2004/06/29 00:40:23 nagayoshi Exp $
#include "flashdevdrv.h"
#include "flashm16c.h"
#ifndef M16C_SERIES
#error "This file is only for M16C."
#endif
/*! Protect flash status */
struct LockBitStatus fmr_status = {0,0};
:SlowMCU()
        :In order to rewrite a flash memory, the clock of MCU operation is made late.
         (Flash Accsess time nomal -> slow)
Arguments :address in area to save CPU clock setting.
Return
       :None
       :It depends on your system.
         You must modify this function for your system.
         This function is the example of "M16C/26 Xin=20MHz."
*************************
void SlowMCU(ProcessorMode * save)
{
  asm("FCLR I");
  save->p_cm0 = cm0;
                 // Save current CPU clock setting
  save->p_cm1 = cm1;
  save->p_pm1 = pm1;
/* "Modify for your system. This code is sample for M16C/26 Xin=20MHz." */
               // Unprotect registers CMO and PMO
// Use Xin, Xin drive HIGH, Xin/2 (f2)
  prcr = 3;
  //
               // CM16 and CM17 are valid
// enable flash data block 1 wait access
  pm17 = 1;
  prcr = 0;
                 // Protection register back on
  asm("FSET I");
:RestoreMCU()
        :Restore MCU clock.
Arguments :address in area to load CPU clock setting.
       :None
       :It depends on your system.
         You must modify this function for your system.
         This function is the example of "M16C/26 Xin=20MHz."
void RestoreMCU(ProcessorMode * save)
  asm("FCLR I");
   prcr = 3;
                 // Unprotect registers CMO and PMO
```

```
pm1 = save->p_pm1;
   cm1 = save->p_cm1;
   cm0 = save->p_cm0;
   prcr = 0;
                    // Protection register back on
   asm("FSET I");
:UnlockBlockFlash()
          :Disable write protect.
Arguments :F_BLOCK_0,F_BLOCK_1,F_ALLBLOCK
                                        All area writing is possible.
          F_BLOCK_2,F_BLOCK_3,F_BLOCK_4,F_BLOCK_5
                   Block2 to 4 area writing is possible.(only M16C/26A,28,29)
        :None
Return
        :It depends on your system.
void UnlockBlockFlash(enum FlashBlock blockNumber)
#if (defined(M16_26A) || defined(M16_28) || defined(M16_29))
  ProcessorMode save_dat;
#endif
   asm("FCLR I");
   switch(blockNumber){
   case F_BLOCK_0: case F_BLOCK_1: case F_ALLBLOCK:
      fmr_status.s_fmr02 = 1;
       /* Not break */
   #if (defined(M16_26A) || defined(M16_28) || defined(M16_29))
   case F_BLOCK_2: case F_BLOCK_3: case F_BLOCK_4: case F_BLOCK_5:
      SlowMCU(&save_dat); // Must change main clock speed to meet flash
      _FLASH_E_EW();
      fmr16 = 0;
      fmr16 = 1;
       _FLASH_DIS_EW();
                             // Restore clock back to original speed
      RestoreMCU(&save_dat);
   #endif
     case F_ALLBLOCK: case F_BLOCK_A : case F_BLOCK_B :
   default:
      break;
   asm("FSET I");
/**********************************
        :LockBlockFlash()
Name
          :Enable write protect.
Arguments :F_BLOCK_0,F_BLOCK_1
                                     Block0,1 are locked.
          F_BLOCK_2,F_BLOCK_3,F_BLOCK_4,F_BLOCK_5
                                      all area is locked.
          F_BLOCK_A,F_BLOCK_B don't have bit for write to lock.
Return
          :None
          :It depends on your system.
*******************
void LockBlockFlash(enum FlashBlock blockNumber)
#if (defined(M16_26A) || defined(M16_28) || defined(M16_29))
ProcessorMode save_dat;
#endif
   asm("FCLR I");
   switch(blockNumber){
   #if (defined(M16_26A) || defined(M16_28) || defined(M16_29))
   case F_BLOCK_2: case F_BLOCK_3: case F_BLOCK_4: case F_BLOCK_5: case F_ALLBLOCK:
      SlowMCU(&save_dat); // Must change main clock speed to meet flash
      _FLASH_E_EW();
      fmr16 = 0;
      _FLASH_DIS_EW();
```



```
RestoreMCU(&save_dat);
                           // Restore clock back to original speed
      /* not break */
   #endif
   case F_BLOCK_0: case F_BLOCK_1:
     fmr_status.s_fmr02 = 0;
   case F_ALLBLOCK: case F_BLOCK_A : case F_BLOCK_B :
   default:
     break;
   asm("FSET I");
Name :SetUpLockBit()
Purpose :set up lock bit.
Notice :It depends on your system.
void SetUpLockBit(void)
   if(fmr_status.s_fmr02){
     fmr02 = 0;
     fmr02 = 1;
   }
}
```

5.1.6 ncrt0_EW0.a30

```
; C COMPILER for R8C/Tiny, M16C/60,30,20,10
; COPYRIGHT(C) 1999(2000-2002) RENESAS TECHNOLOGY CORPORATION
; AND RENESAS SOLUTIONS CORPORATION ALL RIGHTS RESERVED
; ncrt0.a30 : NC30 startup program
; This program is applicable when using the basic I/O library
; $Id: ncrt0_EW0.a30,v 1.4 2004/06/29 00:40:22 nagayoshi Exp $
; HEEP SIZE definition
;-----
   __HEAP__ == 1
.if
HEAPSIZE .equ
.if __HEAPSIZE__ == 0
HEAPSIZE .equ 50H
.else
HEAPSIZE .equ __HEAPSIZE__
.endif
.endif
;-----
; STACK SIZE definition
;-----
.if __USTACKSIZE__ == 0
STACKSIZE .equ
            300h
.else
STACKSIZE .equ __USTACKSIZE__
.endif
; INTERRUPT STACK SIZE definition
;______
    __ISTACKSIZE__ == 0
ISTACKSIZE .equ 300h
ISTACKSIZE .equ __ISTACKSIZE__
.endif
; INTERRUPT VECTOR ADDRESS definition
.if ___R8C___ != 1
            0ffd00h
;VECTOR_ADR .equ
            0ff700h
VECTOR_ADR .equ
.else
VECTOR_ADR .equ
            0fedch
.endif
;_________
; Section allocation
   .list OFF
   .include sect30_EW0.inc
   .list ON
```

```
; SBDATA area definition
    .glb __SB__
__SB__
         .equ data_SE_top
; Initialize Macro declaration
N_BZERO
           .macro TOP_ ,SECT_
    mov.b #00H, R0L
    mov.w #(TOP_ & OFFFFH), A1
    mov.w #sizeof SECT_ , R3
     .endm
N_BCOPY .macro
                FROM_,TO_,SECT_
    mov.w #(FROM_ & OFFFFH),A0
     mov.b #(FROM_ >>16),R1H
    mov.w #TO_ ,A1
mov.w #sizeof SECT_ , R3
     smovf.b
     .endm
BZERO .macro TOP_,SECT_
    push.w #sizeof SECT_ >> 16
    push.w #sizeof SECT_ & Offffh
    pusha TOP_ >>16
pusha TOP_ & Offffh
     .stk 8
     .glb _bzero
     .call _bzero,G
     jsr.a _bzero
     .endm
BCOPY .macro FROM_ ,TO_ ,SECT_
    push.w #sizeof SECT_ >> 16
     push.w #sizeof SECT_ & Offffh
     pusha TO_ >>16
    pusha TO_ & Offffh
           FROM_ >>16
FROM_ & Offffh
     pusha
     pusha
    .stk
           12
     .glb _bcopy
     .call _bcopy,G
     jsr.a
          _bcopy
     .endm
.if ___R8C___ != 1
; for M16C/60,30,20,10 series
           .glb
                 __BankSelect
;__BankSelect
              .equ OBH
; special page definition
     macro define for special page
;Format:
  SPECIAL number
SPECIAL
           .macro NUM
     .org OFFFFEH-(NUM*2)
     .glb __SPECIAL_@NUM
           ___SPECIAL_@NUM & OFFFFH
```



```
; Interrupt section start
;-----
   .insf start,S,0
   .glb
        start
   .section
start:
; after reset, this program will start
        #istack_top, isp ;set istack pointer
   ldc
   mov.b #03h,0ah
   mov.b #00h,04h
                       ;set processer mode
   mov.b #00100000B,07h ;set CM1
   mov.b #0000000B,06h ;set CM0
   mov.b #0000000B,0Ch ;set CM2
   mov.b #00h,0ah
        #0080h, flg
   ldc
   ldc
        #stack_top,
                  sp
                        ;set stack pointer
        #data_SE_top, sb ;set sb register
   ldc
   ldintb #VECTOR ADR
;------
; Program RAM Initialize
;-----
; program area
  N_BCOPY _from_addr,_program_ram_top,program_ram
; vector area
  N_BCOPY VECTOR_ADR,_vector_table,vector_ram
   ldintb # vector table
   ldc #(_vector_table >> 16),INTBH
  ldc #(_vector_table & OFFFFh),INTBL
; NEAR area initialize.
; bss zero clear
   N_BZERO bss_SE_top,bss_SE
   N_BZERO bss_SO_top,bss_SO
   N_BZERO bss_NE_top,bss_NE
   N_BZERO bss_NO_top,bss_NO
; initialize data section
   N_BCOPY data_SEI_top,data_SE_top,data_SE
   N_BCOPY data_SOI_top,data_SO_top,data_SO
   N_BCOPY data_NEI_top,data_NE_top,data_NE
   N_BCOPY data_NOI_top,data_NO_top,data_NO
; FAR area initialize.
; bss zero clear
;-----
   BZERO bss_FE_top,bss_FE
   BZERO bss_FO_top,bss_FO
; Copy edata_E(0) section from edata_EI(0I) section
;-----
   BCOPY data_FEI_top,data_FE_top,data_FE
   BCOPY data_FOI_top,data_FO_top,data_FO
```



```
ldc
       #stack_top,sp
   .stk
; heap area initialize
.if __HEAP__ != 1
   .glb __mbase
   .glb __mnext
   .glb
       __msize
   mov.w #(heap_top&0FFFFH), __mbase
   mov.w
       #(heap_top>>16), __mbase+2
   mov.w #(heap_top&0FFFFH), __mnext
   mov.w #(heap_top>>16), __mnext+2
   mov.w #(HEAPSIZE&OFFFFH), __msize
   mov.w #(HEAPSIZE>>16), __msize+2
.endif
; Initialize standard I/O
;-----
.if __STANDARD_IO__ != 1
   .glb _init
   .call _init,G
   jsr.a _init
.endif
; Call main() function
;-----
   ldc #0h,fb ; for debuger
       _main
   .glb
   jsr.a _main
.else; __R8C__
;-----
; for R8C/Tiny
;______
;------
; Interrupt section start
;-----
   .insf start,S,0
   .glb
       start
   .section
           interrupt
start:
; after reset, this program will start
;------
   ldc
       #istack_top, isp ;set istack pointer
   mov.b #02h,0ah
   mov.b #00h,04h
                   ;set processer mode
   mov.b #00h,0ah
   ldc #0080h, flg
  ldc #stack_top, sp ;set stack pointer
ldc #data_SE_top, sb ;set sb register
   ldintb #VECTOR_ADR
; NEAR area initialize.
; bss zero clear
   N_BZERO bss_SE_top,bss_SE
```



```
N_BZERO bss_SO_top,bss_SO
   N_BZERO bss_NE_top,bss_NE
   N_BZERO bss_NO_top,bss_NO
; initialize data section
   N_BCOPY data_SEI_top,data_SE_top,data_SE
   N_BCOPY data_SOI_top,data_SO_top,data_SO
   N_BCOPY data_NEI_top, data_NE_top, data_NE
   N_BCOPY data_NOI_top, data_NO_top, data_NO
; FAR area initialize.
; bss zero clear
  BZERO bss_FE_top,bss_FE
   BZERO bss_FO_top,bss_FO
; Copy edata_E(O) section from edata_EI(OI) section
  BCOPY data_FEI_top,data_FE_top,data_FE
 BCOPY data_FOI_top,data_FO_top,data_FO
   ldc
        #stack_top,sp
   .stk
        -40
; heap area initialize
.if ___HEAP___ != 1
        __mnext
   .glb
        __msize
   .alb
   mov.w #(heap_top&0FFFFH), __mbase
   mov.w #(heap_top&0FFFFH), __mnext
   mov.w #(HEAPSIZE&OFFFFH), __msize
.endif
; Program RAM Initialize
;-----
; program area
  N_BCOPY _from_addr,_program_ram_top,program_ram
; vector area
  N_BCOPY VECTOR_ADR,_vector_table,vector_ram
   ldc #(_vector_table >> 16),INTBH
   ldc #(_vector_table & OFFFFh),INTBL
; Initialize standard I/O
;-----
.if __STANDARD_IO__ != 1
   .glb _init
   .call _init,G
   jsr.a _init
.endif
; Call main() function
       #0h,fb ; for debuger
```



```
.glb _main
  jsr.a _main
.endif
     ; ___R8C__
; exit() function
  .glb _exit
  .glb $exit
_exit:
               ; End program
$exit:
  jmp _exit
.einsf
; dummy interrupt function
;-----
dummy_int:
  reit
  .end
; C COMPILER for R8C/Tiny, M16C/60,30,20,10 \,
; COPYRIGHT(C) 1999(2000-2002) RENESAS TECHNOLOGY CORPORATION
; AND RENESAS SOLUTIONS CORPORATION ALL RIGHTS RESERVED
```

5.1.7 sect30_EW0.inc

```
; C Compiler for R8C/Tiny, M16C/60,30,20,10
; COPYRIGHT(C) 1999(2000-2002) RENESAS TECHNOLOGY CORPORATION
; AND RENESAS SOLUTIONS CORPORATION ALL RIGHTS RESERVED
; Written by T.Aoyama
; sect30.inc : section definition
; This program is applicable when using the basic I/O library
; $Id: sect30_EW0.inc,v 1.1 2004/06/25 01:29:56 nagayoshi Exp $
.if ___R8C___ != 1
   for M16C/60,30,20,10
;-----
  Arrangement of section
; Near RAM data area
; SBDATA area
   .section
            data_SE,DATA
   .org 400H
data_SE_top:
          bss_SE,DATA,ALIGN
   .section
bss_SE_top:
            data_SO,DATA
   .section
data_SO_top:
             bss_SO,DATA
   .section
bss_SO_top:
; near RAM area
   .section
            data_NE,DATA,ALIGN
data_NE_top:
            bss_NE,DATA,ALIGN
   .section
bss_NE_top:
            data_NO,DATA
   .section
data_NO_top:
            bss_NO,DATA
   .section
bss_NO_top:
;-----
; Stack area
;-----
   .section stack,DATA
   .blkb STACKSIZE
stack_top:
   .blkb ISTACKSIZE
istack_top:
;-----
```

```
heap section
;-----
   .section heap,DATA
heap_top:
   .blkb HEAPSIZE
; RAM program area
   .section program_ram,ALIGN
_program_ram_top:
   .glb _program_ram_top
; RAM vector area
           _____
  .section vector_ram,data,ALIGN
  .ALIGN
_vector_table:
  .blkl 64
       _vector_table
   .glb
; Near ROM data area
   .section rom_NE,ROMDATA
   .org 0f000H
rom_NE_top:
   .section rom_NO,ROMDATA
rom_NO_top:
; Far RAM data area
;______
   .section data_FE,DATA
.org 10000H
   .org
data_FE_top:
          bss_FE,DATA,ALIGN
   .section
bss_FE_top:
            data_FO,DATA
   .section
data_FO_top:
             bss_F0,DATA
   .section
bss_FO_top:
; Far ROM data area
;-----
          rom_FE,ROMDATA
    .section
              0F8000H
   .org
rom_FE_top:
   .section rom_FO,ROMDATA
rom_FO_top:
; Initial data of 'data' section
;-----
             data_SEI,ROMDATA
   .section
data_SEI_top:
          data_SOI,ROMDATA
   .section
data_SOI_top:
```



```
.section
                 data_NEI,ROMDATA
data_NEI_top:
                 data_NOI,ROMDATA
     .section
data_NOI_top:
    .section
                 data_FEI,ROMDATA
data_FEI_top:
     .section
                 data_FOI,ROMDATA
data_FOI_top:
; Switch Table Section
;-----
    .section switch_table,ROMDATA
switch_table_top:
;-----
; code area
     .section
                program
              interrupt
     .section
     .section
             program_S
; variable vector section
     .section vector, ROMDATA; variable vector table
     .org VECTOR_ADR
.if M60TYPE == 1
     .lword dummy_int
                              ; vector 0 (BRK)
                              ; vector 1
     .lword dummy_int
     .lword dummy_int
                               ; vector 2
                              ; vector 3
     .lword dummy_int
                              ; vector 4
     .lword dummy_int
     .lword dummy_int
                              ; vector 5
     .lword dummy_int
                              ; vector 6
     .lword dummy_int
                              ; vector 7
     .lword dummy_int
                              ; vector 8
     .lword dummy_int
                               ; vector 9
                              ; vector 10
     .lword dummy_int
                              ; DMA0 (for user) (vector 11)
     .lword dummy_int
     .lword dummy_int
                              ; DMA1 2 (for user) (vector 12)
     .lword dummy_int
                              ; input key (for user) (vector 13)
     .lword dummy_int
                              ; AD Convert (for user) (vector 14)
                              ; vector 15
     .lword dummy_int
     .lword dummy_int
                               ; vector 16
                              ; uart0 trance (for user) (vector 17)
     .lword dummy_int
                              ; uart0 receive (for user) (vector 18)
     .lword dummy_int
     .lword dummy_int
                              ; uart1 trance (for user) (vector 19)
     .lword dummy_int
                              ; uart1 receive (for user) (vector 20)
                              ; TIMER A0 (for user) (vector 21)
     .lword dummy_int
     .lword dummy_int
                               ; TIMER Al (for user) (vector 22)
     .lword dummy_int
                               ; TIMER A2 (for user) (vector 23)
                              ; TIMER A3 (for user) (vector 24)
     .lword dummy_int
     .lword dummy_int
                              ; TIMER A4 (for user) (vector 25)
     .lword dummy_int
                              ; TIMER B0 (for user) (vector 26)
     .lword dummy_int
                              ; TIMER B1 (for user) (vector 27)
     .lword dummy_int
                               ; TIMER B2 (for user) (vector 28)
     .lword dummy_int
                               ; INTO (for user) (vector 29)
```



```
; INT1 (for user) (vector 30)
                 .lword dummy_int
                 .lword dummy_int
                                                                                                                     ; INT2 (for user) (vector 31)
                 .glb
                                       _timerA1_int
                 .glb _vec_dummy_int
.lword _vec_dummy_int
                                                                                                                    ; BRK (vector 0)
                .lword _vec_dummy_int
.lword _vec_dummy_int
.lword _vec_dum
             .lword _vec_dummy_int ; (vector 1)
.lword _vec_dummy_int ; (vector 2)
.lword _vec_dummy_int ; (vector 3)
.lword _vec_dummy_int ; (vector 3)
.lword _vec_dummy_int ; int3(for user)(vector 4)
.lword _vec_dummy_int ; timerB5(for user)(vector 5)
.lword _vec_dummy_int ; timerB4(for user)(vector 6)
.lword _vec_dummy_int ; timerB4(for user)(vector 7)
.lword _vec_dummy_int ; si/o3 /int4(for user)(vector 9)
.lword _vec_dummy_int ; DMAO(for user)(vector 9)
.lword _vec_dummy_int ; DMAO(for user)(vector 11)
.lword _vec_dummy_int ; Key input interrupt(for user)(vect 13)
.lword _vec_dummy_int ; uart2 transmit(for user)(vect 14)
.lword _vec_dummy_int ; uart2 transmit(for user)(vector 17)
.lword _vec_dummy_int ; uart2 transmit(for user)(vector 17)
.lword _vec_dummy_int ; uart1 transmit(for user)(vector 18)
.lword _vec_dummy_int ; uart2 transmit(for user)(vector 19)
.lword _vec_dummy_int ; uart1 transmit(for user)(vector 19)
.lword _vec_dummy_int ; uart1 receive(for user)(vector 20)
.lword _vec_dummy_int ; timer A1(for user)(vector 22)
.lword _vec_dummy_int ; timer A2(for user)(vector 23)
.lword _vec_dummy_int ; timer A2(for user)(vector 23)
.lword _vec_dummy_int ; timer A2(for user)(vector 24)
.lword _vec_dummy_int ; timer B1(for user)(vector 25)
.lword _vec_dummy_int ; timer B2(for user)(vector 27)
.lword _vec_dummy_int ; timer B2(for user)(vector 28)
.lword _vec_dummy_int ; timer B2(for user)(vector 28)
.lword _vec_dummy_int ; timer B2(for user)(vector 28)
.lword _vec_dummy_int ; timer B2(for user)(vector 29)
.lword _vec_dummy_int ; timer B2(for user)(vector 30)
.lword _vec_dummy_int ; timer B2(for user)(vector 31)
.lword _vec_dummy_int ; timer B2(for user)(vector 31)
.lword _vec_dummy_int ; int1 (for user)(vector 31)
.lword _vec_dummy_int ; int2 (for user) vector 32
                                                                                                                                             (vector 1)
                                                                                                                                          (vector 2)
                                                                                                               ;
                                                                                      ; vector 32 (for user or MR30)
; vector 33 (for user or MR30)
; vector 34 (for user or MR30)
; vector 35 (for user or MR30)
; vector 36 (for user or MR30)
; vector 37 (for user or MR30)
; vector 38 (for user or MR30)
; vector 39 (for user or MR30)
; vector 40 (for user or MR30)
; vector 41 (for user or MR30)
; vector 42 (for user or MR30)
; vector 43 (for user or MR30)
; vector 44 (for user or MR30)
; vector 45 (for user or MR30)
; vector 46 (for user or MR30)
; vector 47 (for user or MR30)
; vector 48
; vector 49
endif
                 .lword dummy_int
                 .lword dummy int
                 .lword dummy_int
                 .lword dummy int
                                                                                                               ; vector 49
                 .lword dummy_int
                 .lword dummy_int
                                                                                                               ; vector 50
                 .lword dummy_int
                                                                                                               ; vector 51
                                                                                                               ; vector 52
                 .lword dummy_int
                                                                                                                 ; vector 53
; vector 54
                 .lword dummy_int
                 .lword dummy_int
                                                                                                                ; vector 55
                 .lword dummy_int
                 .lword dummy_int
                                                                                                               ; vector 56
                 .lword dummy_int
                                                                                                               ; vector 57
                 .lword dummy_int
                                                                                                                ; vector 58
                 .lword dummy_int
                                                                                                                  ; vector 59
                 .lword dummy_int
                                                                                                                     ; vector 60
```



```
.lword dummy_int
                           ; vector 61
                     ; vector 62
    .lword dummy_int
    .lword dummy_int
                           ; vector 63
; fixed vector section
   .section fvector, ROMDATA
                                            ; fixed vector table
; special page defination
;______
   macro is defined in ncrt0.a30
   Format: SPECIAL number
  SPECIAL 255
  SPECIAL 254
  SPECIAL 253
  SPECIAL 252
;
   SPECIAL 251
   SPECIAL 250
  SPECIAL 249
  SPECIAL 248
;
  SPECIAL 247
  SPECIAL 246
;
  SPECIAL 245
   SPECIAL 244
  SPECIAL 243
  SPECIAL 242
  SPECIAL 241
  SPECIAL 240
   SPECIAL 239
;
   SPECIAL 238
   SPECIAL 237
   SPECIAL 236
  SPECIAL 235
  SPECIAL 234
;
  SPECIAL 233
   SPECIAL 232
;
   SPECIAL 231
   SPECIAL 230
  SPECIAL 229
  SPECIAL 228
  SPECIAL 227
  SPECIAL 226
   SPECIAL 225
;
   SPECIAL 224
   SPECIAL 223
   SPECIAL 222
  SPECIAL 221
  SPECIAL 220
  SPECIAL 219
;
   SPECIAL 218
;
   SPECIAL 217
   SPECIAL 216
  SPECIAL 215
  SPECIAL 214
  SPECIAL 213
   SPECIAL 212
;
   SPECIAL 211
   SPECIAL 210
   SPECIAL 209
   SPECIAL 208
  SPECIAL 207
;
  SPECIAL 206
   SPECIAL 205
;
   SPECIAL 204
```



```
SPECIAL 203
  SPECIAL 202
  SPECIAL 201
  SPECIAL 200
    SPECIAL 199
;
    SPECIAL 198
    SPECIAL 197
    SPECIAL 196
   SPECIAL 195
  SPECIAL 194
;
  SPECIAL 193
    SPECIAL 192
;
    SPECIAL 191
    SPECIAL 190
   SPECIAL 189
  SPECIAL 188
  SPECIAL 187
   SPECIAL 186
;
    SPECIAL 185
;
    SPECIAL 184
    SPECIAL 183
;
   SPECIAL 182
  SPECIAL 181
;
  SPECIAL 180
  SPECIAL 179
;
   SPECIAL 178
;
    SPECIAL 177
   SPECIAL 176
;
   SPECIAL 175
  SPECIAL 174
  SPECIAL 173
   SPECIAL 172
;
    SPECIAL 171
    SPECIAL 170
    SPECIAL 169
   SPECIAL 168
  SPECIAL 167
  SPECIAL 166
;
    SPECIAL 165
;
    SPECIAL 164
    SPECIAL 163
   SPECIAL 162
  SPECIAL 161
  SPECIAL 160
  SPECIAL 159
;
    SPECIAL 158
;
    SPECIAL 157
;
    SPECIAL 156
   SPECIAL 155
;
   SPECIAL 154
  SPECIAL 153
  SPECIAL 152
;
    SPECIAL 151
;
    SPECIAL 150
   SPECIAL 149
   SPECIAL 148
  SPECIAL 147
;
  SPECIAL 146
    SPECIAL 145
;
    SPECIAL 144
    SPECIAL 143
    SPECIAL 142
;
   SPECIAL 141
   SPECIAL 140
;
  SPECIAL 139
    SPECIAL 138
;
    SPECIAL 137
```



```
SPECIAL 136
  SPECIAL 135
  SPECIAL 134
  SPECIAL 133
    SPECIAL 132
;
    SPECIAL 131
    SPECIAL 130
   SPECIAL 129
  SPECIAL 128
  SPECIAL 127
;
  SPECIAL 126
   SPECIAL 125
;
    SPECIAL 124
   SPECIAL 123
   SPECIAL 122
  SPECIAL 121
  SPECIAL 120
  SPECIAL 119
;
    SPECIAL 118
;
    SPECIAL 117
   SPECIAL 116
;
   SPECIAL 115
  SPECIAL 114
;
  SPECIAL 113
  SPECIAL 112
;
   SPECIAL 111
;
    SPECIAL 110
   SPECIAL 109
;
   SPECIAL 108
  SPECIAL 107
  SPECIAL 106
   SPECIAL 105
;
    SPECIAL 104
    SPECIAL 103
   SPECIAL 102
   SPECIAL 101
  SPECIAL 100
  SPECIAL 99
;
   SPECIAL 98
;
    SPECIAL 97
   SPECIAL 96
  SPECIAL 95
;
  SPECIAL 94
  SPECIAL 93
  SPECIAL 92
;
    SPECIAL 91
;
    SPECIAL 90
;
    SPECIAL 89
   SPECIAL 88
;
  SPECIAL 87
  SPECIAL 86
  SPECIAL 85
;
   SPECIAL 84
;
    SPECIAL 83
   SPECIAL 82
  SPECIAL 81
  SPECIAL 80
  SPECIAL 79
;
   SPECIAL 78
;
    SPECIAL 77
    SPECIAL 76
    SPECIAL 75
;
   SPECIAL 74
   SPECIAL 73
;
  SPECIAL 72
    SPECIAL 71
;
    SPECIAL 70
```



```
SPECIAL 69
;
  SPECIAL 68
  SPECIAL 67
   SPECIAL 66
    SPECIAL 65
;
    SPECIAL 64
    SPECIAL 63
   SPECIAL 62
;
   SPECIAL 61
  SPECIAL 60
  SPECIAL 59
;
   SPECIAL 58
;
    SPECIAL 57
   SPECIAL 56
   SPECIAL 55
   SPECIAL 54
  SPECIAL 53
   SPECIAL 52
;
    SPECIAL 51
;
    SPECIAL 50
    SPECIAL 49
;
   SPECIAL 48
;
   SPECIAL 47
;
  SPECIAL 46
   SPECIAL 45
;
   SPECIAL 44
;
    SPECIAL 43
   SPECIAL 42
;
   SPECIAL 41
   SPECIAL 40
   SPECIAL 39
   SPECIAL 38
;
;
    SPECIAL 37
    SPECIAL 36
   SPECIAL 35
;
   SPECIAL 34
  SPECIAL 33
  SPECIAL 32
;
   SPECIAL 31
;
    SPECIAL 30
   SPECIAL 29
   SPECIAL 28
   SPECIAL 27
  SPECIAL 26
   SPECIAL 25
;
    SPECIAL 24
;
    SPECIAL 23
;
    SPECIAL 22
   SPECIAL 21
;
   SPECIAL 20
   SPECIAL 19
    SPECIAL 18
; fixed vector section
     .org Offfdch
UDI:
    .lword dummy_int
OVER_FLOW:
    .lword dummy_int
BRKI:
     .lword dummy_int
ADDRESS_MATCH:
    .lword dummy_int
SINGLE_STEP:
    .lword dummy_int
```



```
WDT:
    .lword dummy_int
DBC:
    .lword dummy_int
NMI:
    .lword dummy_int
    .org
        OffffcH
RESET:
    .lword start
.else; ___R8C__
; for R8C/Tiny
;-----
   Arrangement of section
; Near RAM data area
; SBDATA area
    .section
               data_SE,DATA
    .org 400H
data_SE_top:
              bss_SE,DATA,ALIGN
    .section
bss_SE_top:
    .section
              data_SO,DATA
data_SO_top:
    .section
                bss_S0,DATA
bss_SO_top:
; near RAM area
   .section
              data_NE,DATA,ALIGN
data_NE_top:
    .section
            bss_NE,DATA,ALIGN
bss_NE_top:
   .section
              data_NO,DATA
data_NO_top:
    .section
                bss_NO,DATA
bss_NO_top:
; Stack area
    .section stack, DATA, ALIGN
    .blkb STACKSIZE
stack_top:
    .blkb ISTACKSIZE
istack_top:
  heap section
;-----
   .section heap,DATA
heap_top:
    .blkb HEAPSIZE
```



```
; RAM program area
    _____
    .section
              program_ram,ALIGN
_program_ram_top:
    .glb _program_ram_top
; RAM vector area
  .section vector_ram,data,ALIGN
   .ALIGN
_vector_table:
   .blkl 64
         _vector_table
    .glb
;-----
; Near ROM data area
;-----
    .section rom_NE,ROMDATA
.org 0e000H
rom_NE_top:
    .section
              rom_NO,ROMDATA
rom_NO_top:
; Initial data of 'data' section
            data_SEI,ROMDATA,ALIGN
    .section
data_SEI_top:
              data_SOI,ROMDATA
    .section
data_SOI_top:
               data_NEI,ROMDATA,ALIGN
    .section
data_NEI_top:
    .section
           data_NOI,ROMDATA
data_NOI_top:
;______
; Switch Table Section
   .section switch_table,ROMDATA
switch_table_top:
; code area
    .section program, CODE, ALIGN
    .section
              interrupt, CODE, ALIGN
; variable vector section
    .section vector,ROMDATA ; variable vector table
    .org VECTOR_ADR
    .glb
         _int_timerx
    .lword dummy_int
                           ; vector 0
    .lword dummy_int
                          ; vector 1
    .lword dummy_int
                          ; vector 2
    .lword dummy_int
                          ; vector 3
    .lword dummy_int
                           ; vector 4
    .lword dummy_int
                           ; vector 5
```



```
| vector 7 | vector 8 | vector 9 | vector 10 | vector 11 | vector 11 | vector 11 | vector 12 | vector 13 | vector 15 | vector 15 | vector 15 | vector 16 | vector 17 | vector 18 | vector 17 | vector 18 | vector 19 | vector 20 | vector 21 | vector 21 | vector 21 | vector 23 | vector 24 | vector 25 | vector 26 | vector 27 | vector 26 | vector 27 | vector 28 | vector 29 | vector 30 | vector 31 | vector 31 | vector 32 | vector 34 | vector 34 | vector 35 | vector 36 | vector 37 | vector 38 | vector 39 | vector 39 | vector 39 | vector 39 | vector 40 | vector 40 | vector 41 | vector 42 | vector 42 | vector 45 | vector 46 | vector 47 | vector 40 | vector 47 | vector 47 | vector 47 | vector 47 | vector 40 | vector 
                    .lword dummy_int
                                                                                                                               ; vector 6
                                                                                                                            ; vector 51
; vector 52
; vector 53
                    .lword dummy_int
                    .lword dummy_int
                                                                                                                             ; vector 54
                   .lword dummy_int
                                                                                                                             ; vector 55
                   .lword dummy_int
                   .lword dummy_int
                                                                                                                             ; vector 56
                                                                                                                           ; vector 57
; vector 58
; vector 59
; vector 60
                    .lword dummy_int
                   .lword dummy_int
                    .lword dummy_int
                    .lword dummy_int
                   .lword dummy_int
                                                                                                                            ; vector 61
                   .lword dummy_int
                                                                                                                             ; vector 62
                    .lword dummy_int
                                                                                                                                ; vector 63
; fixed vector section
;-----
                .section fvector, ROMDATA
                                                                                                                                                                                    ; fixed vector table
                  .org OffdcH
;UDI:
; .lword dummy_int
;OVER_FLOW:
```



```
.lword dummy_int
;BRKI:
   .lword dummy_int
;ADDRESS_MATCH:
   .lword dummy_int
;SINGLE_STEP:
; .lword dummy_int
; WDT:
    .lword dummy_int
    .lword dummy_int
;NMI:
    .lword dummy_int
    .org OfffcH
RESET:
    .lword start | OFF000000H
.endif
         ; ___R8C
; far ROM data area
  .section rom_FE,ROMDATA
.org 10000H
;
   .section
            rom_FO,ROMDATA
              data_FEI,ROMDATA,ALIGN
    .section
;data_FEI_top:
    .section
                 data_FOI,ROMDATA
;data_FOI_top:
C Compiler for R8C/Tiny, M16C/60,30,20,10
; COPYRIGHT(C) 1999(2000-2002) RENESAS TECHNOLOGY CORPORATION
; AND RENESAS SOLUTIONS CORPORATION ALL RIGHTS RESERVED
```



5.1.8 main_m16c.c

```
/*
   FILE NAME : main_m16c.c
   Ver : 1.00
/*
/*
    CPU
            : M16C/26
   FUNCTION : Data Flash rewrite Apllication Note sample program */
              for EWO mode operation
/*-----*/
/* Copyright(C)2004, Renesas Technology Corp.
/* Copyright(C)2004, Renesas Solutions Corp.
/* All rights reserved.
// $Id: main_m16c.c,v 1.6 2004/06/30 02:28:41 nagayoshi Exp $
#include <string.h>
#include <stdio.h>
#include "sfr28.h"
#include "flashdevdrv.h"
#ifndef FALSE
#define FALSE 0
#endif
#ifndef TRUE
#define TRUE 1
#endif
typedef unsigned char BOOL;
#define
        BLOCK_SIZE
                             2048
#pragma INTERRUPT timerAl_int;
void timerAl_int(void);
/*** Interrupt dummy (running on ram) ***/
#pragma INTERRUPT vec_dummy_int;
void far vec_dummy_int(void);
void ErrorDisp(const char * dt);
void mcu_init(void);
int CheckErasedBlank(void F_ADR_SIZE * f_addr, short size);
int CmpBlank(unsigned char F_ADR_SIZE * buf , short size);
/** Timer ******/
/*=======*/
enum TimerSource{
   TIMER_DEV_1 = 0x00,
   TIMER_DEV_8 = 0x40,
   TIMER DEV 32 = 0 \times 80,
   TIMER_SUB_32 = 0xC0,
};
#define TIMER_CLOCK_Hz
                     20000000
#define TIMER_SUBCLOCK_Hz 32768
#define TA1_DEV32_MS(a) ((TIMER_CLOCK_Hz / 32000) * (a) - 1)
#define TA1_DEV8_MS(a) ((TIMER_CLOCK_Hz / 8000) * (a) - 1)
\#define\ TA1\_DEV1\_MS(a)\ ((TIMER\_CLOCK\_Hz\ /\ 1000)\ *\ (a)\ -\ 1)
BOOL CheckTalPassed(void);
void SetTickTimer(unsigned char tm);
void TimerAlInitTimerMode(enum TimerSource source,
                   unsigned short timer);
inline void StartTimerAl(void);
```

```
inline void StartTimerAl(void)
   tals = 1;
                            // TimerAl start
}
void ClearTotalTimer(void);
void SystemTimerInc(void);
/** RAM for Timer **/
BOOL tm_ps = FALSE;
unsigned char tm_ms = 0;
unsigned long totalTimer = 0; // ms
inline unsigned long GetTotalTimer(void);
inline unsigned long GetTotalTimer(void)
   return totalTimer;
/*=======*/
/** Timer End ****/
/*========*/
enum MainMode{
  ERASE_TEST_START,
   ERASE_TEST_RESTART,
   ERASE_TEST_CHECK,
   PROGRAM_TEST,
   OTHER,
} mode = ERASE_TEST_START;
const char TestData[33] = "0123456789ABCDEF0123456789ABCDEF";
/************************
// Main loop
*****************************
void main(void)
   unsigned char buffer_addr[32];
   FlashResult err_code = F_SUCCESS;
   * /
   FlashInitialize(); /* FlashMemory Initialize
   StartTimerA1();
   asm("fset i");
   /* Unlock gives a Flash block to write. (This example is unnecessary.) */
   UnlockBlockFlash(F_BLOCK_3);
   /* example : When a main loop is done in 20mS and made to work.
   The turn of the movement
   mode
                       Address and contents of a test
    << start >>
   ERASE_TEST_START 0xF000-0xF7FF Start Erasing
ERASE_TEST_RESTART 0xF000-0xF7FF Restart Erasing
                       0xF000-0xF7FF Erasing confirmation
   ERASE TEST CHECK
                        0xF000-0xF01F Write and confirmation
   PROGRAM_TEST
   OTHER
                        Wait until it passes from the erasing start for one second.
                         Judge it as the error, and reset a flash memory
                         when erasing isn't completed in one second.
     << Repetition >>
   for(;;){
       /* Waiting 20ms passed */
       while(!CheckTalPassed());
```

```
case ERASE_TEST_START:
        case ERASE_TEST_RESTART:
           /* Start/Restart erasing
                                        * /
            /* So that it may clear a suspend requirement to do ResumErase()
              before resuming elimination.
            if(mode == ERASE_TEST_START){
                ClearTotalTimer(); /* Make totalTimer 0 for the erasing time acquisition. */
                err_code = StartEraseFlash((void F_ADR_SIZE *)0xF7FE);
            else {
                ResumErase();
                err_code = RestartEraseFlash();
            /* Check err code. */
            switch(err_code){
            case F_SUSPEND: mode = ERASE_TEST_RESTART; break;
            case F_SUCCESS: mode = ERASE_TEST_CHECK;
                                                        break;
            default:
                           ErrorDisp("EraseER1");
                                                        break;
            /* TimeOut Check */
            ^{\prime \star} Take an error when F_SUSPEND occurs for one second after you start elimination. ^{\star \prime}
            if(GetTotalTimer() >= 1000){
                if(mode == ERASE_TEST_RESTART){
                    FlashReset();
                                       /* Make condition revert with FlashReset(). */
                    ErrorDisp("Err Tout");
            }
            break;
        case ERASE_TEST_CHECK:
            /* Check whether even an erase block (0xF000-0xF7FFF) is being erased. */
            if(0 == CheckErasedBlank((void F_ADR_SIZE *)0xF000, BLOCK_SIZE)){
                ErrorDisp("EraseER2");
            mode = PROGRAM_TEST;
           break;
        case PROGRAM TEST:
            /* Writing 32byte and error code check
                                                        */
            err_code = WriteFlash((void F_ADR_SIZE *)0xF000, TestData, 32);
            if(err_code != F_SUCCESS)ErrorDisp("WriteERR");
            /* The data being written check whether it begins to read it. */
            err_code = ReadFlash((void F_ADR_SIZE *)0xF000 , buffer_addr, 32);
            if(err_code != F_SUCCESS)ErrorDisp("Read ERR");
            /* Compare data of write and data of read. */
            if(memcmp(buffer_addr , TestData , 32)){
                ErrorDisp("Comp ERR");
            mode = OTHER;
            break;
         default:
            if(GetTotalTimer() >= 1000){
               mode = ERASE_TEST_START;
        }
    }
}
 * Confirm whether a flash memory is in the blank.
 * f_addr : physical address on flash memory to confirm.
 * size : Number of bytes to confirm.
 * return : 1:blank
        : 0:not blank
 ========*/
```

switch(mode){

```
int CheckErasedBlank(void F_ADR_SIZE * f_addr, short size)
   unsigned char F_ADR_SIZE * faddr = f_addr;
   FlashResult err_code = F_SUCCESS;
   unsigned short r_buf[16];
   unsigned short r_size;
   for(; size > 0 ; ){
      r_size = (size > sizeof(r_buf))? sizeof(r_buf):size;
       err_code = ReadFlash(faddr , r_buf , r_size);
       if(CmpBlank((unsigned char F_ADR_SIZE * )r_buf , r_size)){
          return 0;
       }
       faddr += r_size;
       size -= r_size;
   return 1;
}
* Compare the matter whether designated data are "BLANK_PATTERN".
\mbox{*} \mbox{f\_addr} : physical address on flash memory to confirm.
* size : Number of bytes to confirm.
* return : 1:blank
       : 0:not blank
========*/
#define BLANK_PATTERN 0xff
int CmpBlank(unsigned char F_ADR_SIZE * buf , short size)
   while(size --){
       if(* buf ++ != BLANK_PATTERN)return -1;
   return 0;
}
/*----
Error display and cancellation of a movement.
========*/
void ErrorDisp(const char * dt)
    DISPLAY(1, dt);
//
   while(1);
initialize MCU
=======*/
void mcu_init( void )
  /* Select full speed operation */
  /* Switch port initialization */
  pd10_5 = 0;
                // change switch ports to inputs
  pd10_6 = 0;
  pd10_7 = 0;
  /* LED initialization */
  pd7_0 = 1;
                 // Change LED ports to outputs (connected to LEDs)
  pd7_1 = 1;
  pd7_2 = 1;
  /* unused pins - configure as outputs to decrease power consumption */
  pd6 = 0x90;
  pd8_0 = 1;
  pd8_1 = 1;
  pd8_2 = 1;
  pd8_3 = 1;
```



```
prc2 = 1;
                 // P9 is write protected - disable protection before writing to P9
  pd9_0 = 1;
  pd9_1 = 1;
  pd9_2 = 1;
  pd9_3 = 1;
  prc2 = 0;
                // Write protect P9
  pd10_0 = 1;
  pd10_1 = 1;
  pd10_2 = 1;
  pd10_3 = 1;
  pd10_4 = 1;
// Set up a Timer A1
   TimerAlInitTimerMode(TIMER_DEV_32,TA1_DEV32_MS(20));
   SetTickTimer(20);
   talic = 0x07;
                                  // Set Timer-Al Interrupt-Priolity-Level
// Port Initialize
  p6 = 0x00;
                                  // Port-6 clear
   pd6 = 0xff;
                                   // Port-6 is output port
   p7 = 0x07;
                                  // p7_0 - p7_2 LED off
   pd7 = 0x07;
                                  // p7_0 to p7_2 output select
   pu25 = 1;
                                  // p10_4 to P10_7 pull-up
   p10 = 0x00;
                                  // Port-10 clear
   pd10 = 0x1f;
                                  // p10_5 to p10_7 is Key-in port
}
/* Timer
/**********************************
Check tick time.
========*/
BOOL CheckTalPassed(void)
   if(tm_ps){
     tm_ps = FALSE;
      return TRUE;
   return FALSE;
}
Set up value of tick time.
========*/
void SetTickTimer(unsigned char tm)
   tm_ms = tm;
Initialize Timer A1.
========*/
void TimerAlInitTimerMode(enum TimerSource source,
                     unsigned short timer)
// Set up a Timer Al
  tals = 0;
                                  // Timer-Al Stopped
   talic = 0x07;
                                  // Set Timer-Al Interrupt-Priolity-Level
   talmr = source;
                                  // Set Timer-Al mode regster
                                  // Mode=Timer-mode,Count-src=f1
```

```
// Set Timer-Al timer-value (50ms)
  ta1
     = timer;
Clear totaltimer
=======*/
void ClearTotalTimer(void)
  totalTimer = 0;
/****************************
The following is a program to work by the RAM.(EWO only)
************************
#ifdef FLASH_MODE_EW0
#pragma SECTION program program_ram
#endif
Timer Al Interrupt function
========*/
void timerAl_int(void)
  /* Suspend erasing and advance timer. */
  SuspendErase();
  SystemTimerInc();
}
This is function for Timer Al interrupt.
=========*/
void SystemTimerInc(void)
  // 1ms
  tm_ps = TRUE;
  totalTimer += tm_ms;
dummy Interrupt
========*/
void vec_dummy_int(void)
```



5.1.9 M16C EW0.tmk

```
# Makefile for TM V.3.20A
  # COPYRIGHT(C) 1998(1998-2003)
 # RENESAS TECHNOLOGY CORPORATION ALL RIGHTS RESERVED
 # RENESAS SOLUTIONS CORPORATION ALL RIGHTS RESERVED
     Notice :
                  Don't edit.
 #
                  2004 06(June) 25(Friday) AM.10.42
     Date :
      Project:
                  M16C_EW0
  @-del
 LNLTST
                   $(PROJECT).cmd
 FROM_ADDR =
                  0FB000
 LMC = LMC30
 CC =
           NC30
          LB30
ut130
 AR
      =
 UTL =
            AS30
 AS
 LIBFILE
            =
                   $(PROJECT).lib
           =
 OUTDIR
                  M16CEW0
 MKDIR = @-mkdir
 ABSFILE
           =
                  $(PROJECT).x30
 ODINCMD
                   $(OUTDIR)
            LN30
 TARGET
            =
                   $(ABSFILE)
 ECHO =
           @-echo
 MKFILE
                  $(PROJECT).tmk
            =
 PROJECT
                  M16C_EW0
 TYPE =
           @-type
 LFLAGS
           =
                   -MS -L nc30lib -G -LOC program_ram=$(FROM_ADDR) -O $(OUTDIR)\$(TARGET)
 UTLFLAGS
 CFLAGS
            =
                   -c -dir $(OUTDIR) -g -gbool_to_char -OR -O4 -OSA -finfo -fUD -fNA -fSA -WNP -
WUP -WNC -Wall -WUV -WNUA
 LMCFLAGS =
                  -L
 LIBFLAGS
                   -C
            =
 AFLAGS
                  -LM -D__HEAP__=1 -D__STANDARD_IO__=1 -
D_from_addr=$(FROM_ADDR)h:__USTACKSIZE__=160h:__ISTACKSIZE__=160h -finfo -0$(OUTDIR)
  .SUFFIXES: .a30 .r30 .c .x30 .lib
  .PHONY: all
 all: \
            $(OUTDIR)\$(TARGET)
  .PHONY: clean
 clean:
      $(DELETE) $(OUTDIR)\$(TARGET)
      $(DELETE) $(ODINCMD)\$(LNLIST)
      $(DELETE) $(OUTDIR)\ncrt0_EW0.r30
      $(DELETE) $(OUTDIR)\depend m16c.r30
      $(DELETE) $(OUTDIR)\flashdrvdev_ew0.r30
      $(DELETE) $(OUTDIR)\main_m16c.r30
  $(ODINCMD)\$(LNLIST): \
             .\$(MKFILE)
      $(ECHO)\$(MRLFLAGS) $(LFLAGS) >
                                      $(ODINCMD)\$(LNLIST)
      $(ECHO)\$(OUTDIR)\ncrt0_EW0.r30 >> $(ODINCMD)\$(LNLIST)
      $(ECHO)\$(OUTDIR)\depend_m16c.r30 >> $(ODINCMD)\$(LNLIST)
      $(ECHO)\$(OUTDIR)\flashdrvdev_ew0.r30 >>
                                             $(ODINCMD)\$(LNLIST)
      (ECHO)\(OUTDIR)\main_m16c.r30 >> (ODINCMD)\(LNLIST)
  $(OUTDIR)\$(TARGET): \
             $(ODINCMD)\$(LNLIST) \
             $(OUTDIR)\ncrt0_EW0.r30 \
             $(OUTDIR)\depend_m16c.r30 \
             $(OUTDIR)\flashdrvdev_ew0.r30 \
             $(OUTDIR)\main_m16c.r30
      (LN) @$(ODINCMD)\slash(LNLIST)
```



```
$(OUTDIR)\depend_m16c.r30: \
          .\depend_m16c.c \
          .\flashdevdrv.h \
          .\flashdevconf.h \
          .\flashm16c.h
    $(CC) $(MRCFLAGS) $(CFLAGS) depend_ml6c.c
$(OUTDIR)\flashdrvdev_ew0.r30: \
          .\flashdrvdev_ew0.c \
          .\flashdevdrv.h \
          .\flashdevconf.h \
           .\flashm16c.h
    $(CC) $(MRCFLAGS) $(CFLAGS) flashdrvdev_ew0.c
$(OUTDIR)\main_m16c.r30: \
          .\main_m16c.c \
          .\flashdevdrv.h \
          .\flashdevconf.h
    $(CC) $(MRCFLAGS) $(CFLAGS) main_m16c.c
$(OUTDIR)\ncrt0_EW0.r30: \
          .\ncrt0_EW0.a30 \
          .\sect30_EW0.inc
    $(AS) $(MRAFLAGS) $(AFLAGS) ncrt0_EW0.a30
# End of makefile for TM V.3.20A
# COPYRIGHT(C) 1998(1998-2003)
# RENESAS TECHNOLOGY CORPORATION ALL RIGHTS RESERVED
# AND
# RENESAS SOLUTIONS CORPORATION ALL RIGHTS RESERVED
```



6. Reference

Hardware Manual

M16C/26 Group Hardware Manual Rev.0.90

M16C/28 Group Hardware Manual Rev.0.60

M16C/29 Group Hardware Manual Rev.1.00

The latest version can be downloaded from the Renesas Electronics website.

TECHNICAL UPDATE/TECHNICAL NEWS

The latest information can be downloaded from the Renesas Electronics website.

7. Website and Support

Renesas Electronics Website http://www.renesas.com/

Inquiries

http://www.renesas.com/inquiry

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Revision Record

Description

Rev.	Date	Page	Summary
1.00	Mar.16.05	_	First edition issued
1.01	Dec.28.10	9	Figure 3-5 "Auto Erase Flowchart (Reference)" partially modified
		15	Figure 3-10 "Auto Erase Procedure" partially modified
		20	Figure 3-12 "Auto Erase Flowchart for the RAM Reduced Version partially modified
		31	Table 4-3 "StartEraseFlash()" parameter meaning "Beginning address of the flash memory to be erased" → "Highest address of the flash memory to be erased (even address)"
		80	9th line 0xF000 → 0xF7FE

General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

— The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

The state of the product is undefined at the moment when power is supplied.

- The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.
 In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.
 In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.
- 3. Prohibition of Access to Reserved Addresses

Access to reserved addresses is prohibited.

The reserved addresses are provided for the possible future expansion of functions. Do not access
these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

- When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.
- 5. Differences between Products

Before changing from one product to another, i.e. to one with a different type number, confirm that the change will not lead to problems.

— The characteristics of MPU/MCU in the same group but having different type numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different type numbers, implement a system-evaluation test for each of the products.

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